

# *The upgrade of LHCb VELO*



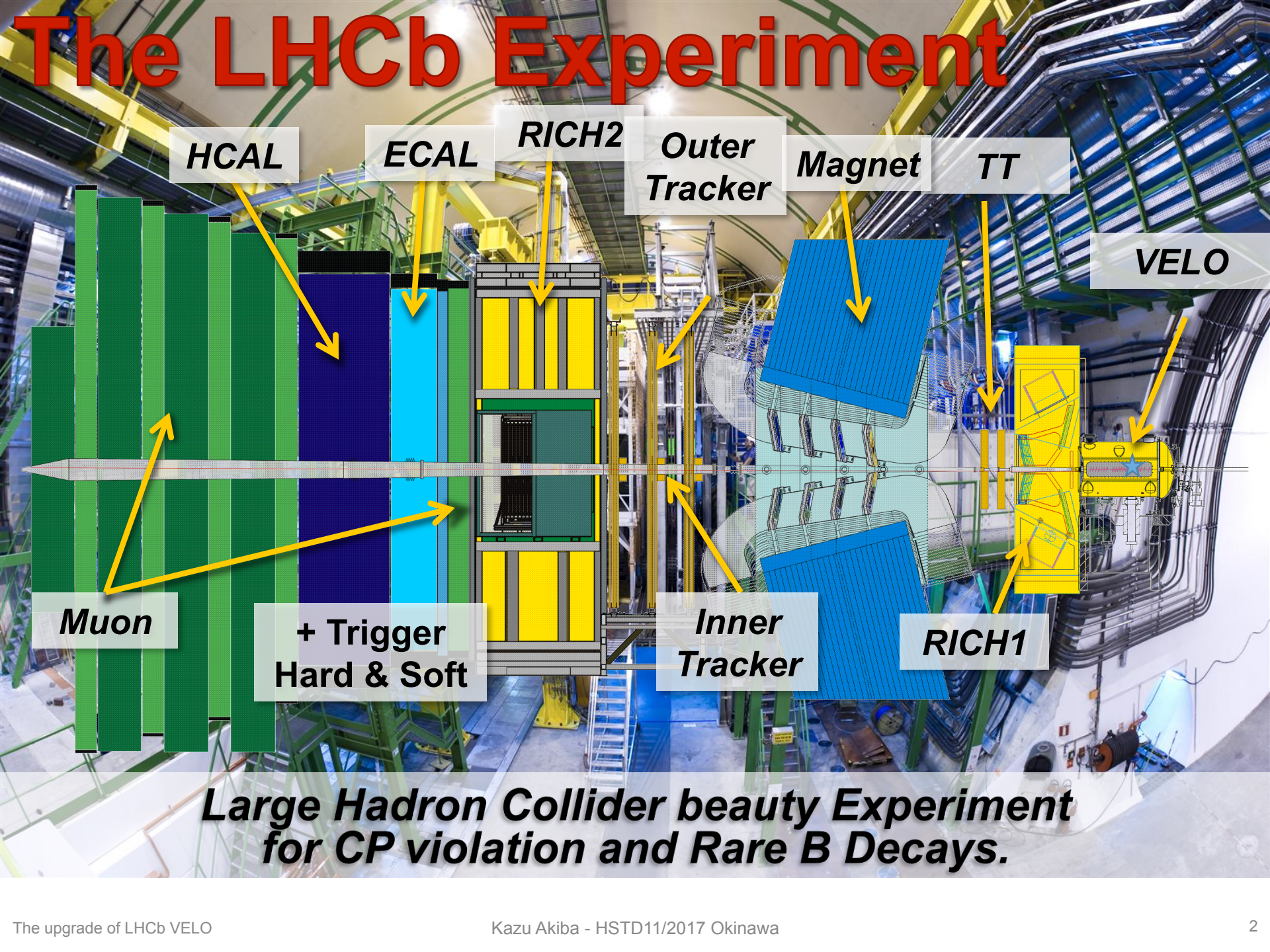
Kazuyoshi Akiba on behalf of the VELO group



UNIVERSIDADE FEDERAL  
DO RIO DE JANEIRO







# The LHCb Experiment

HCAL

ECAL

RICH2

Outer Tracker

Magnet

TT

VELO

Muon

+ Trigger  
Hard & Soft

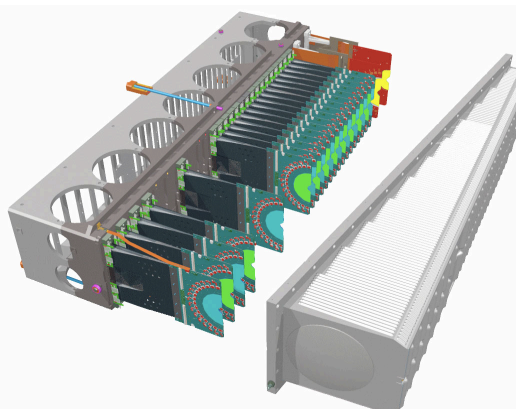
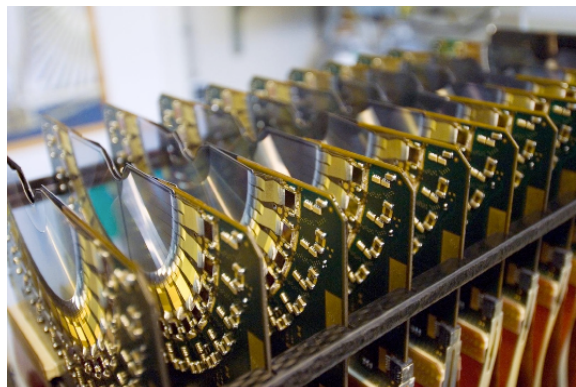
Inner Tracker

RICH1

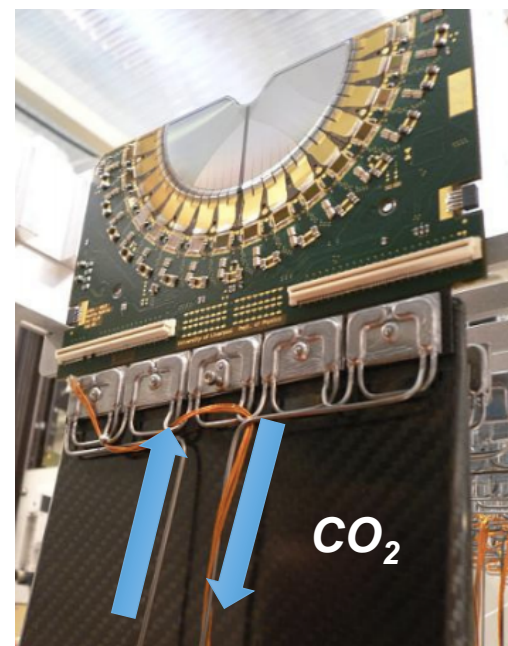
**Large Hadron Collider beauty Experiment  
for CP violation and Rare B Decays.**



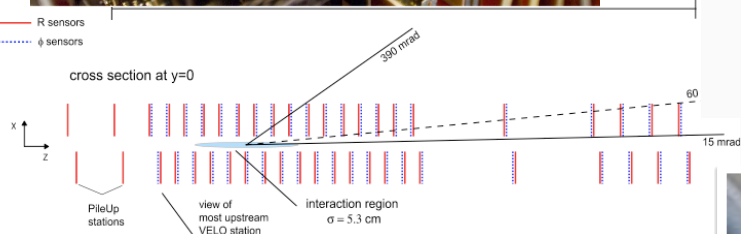
# The current Vertex Locator (VELO):



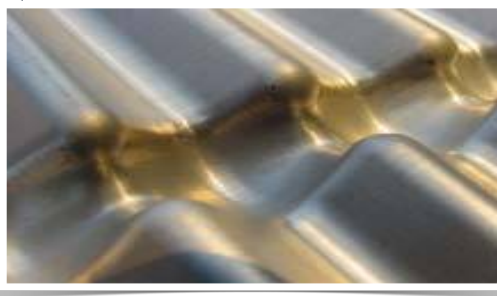
biphase cooling



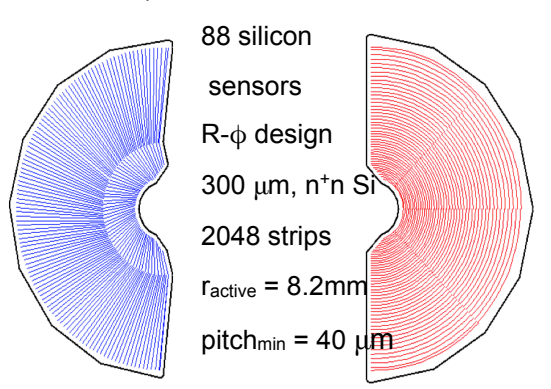
**Evaporation** of CO<sub>2</sub> keeps the temperature stable.



Operates in vacuum



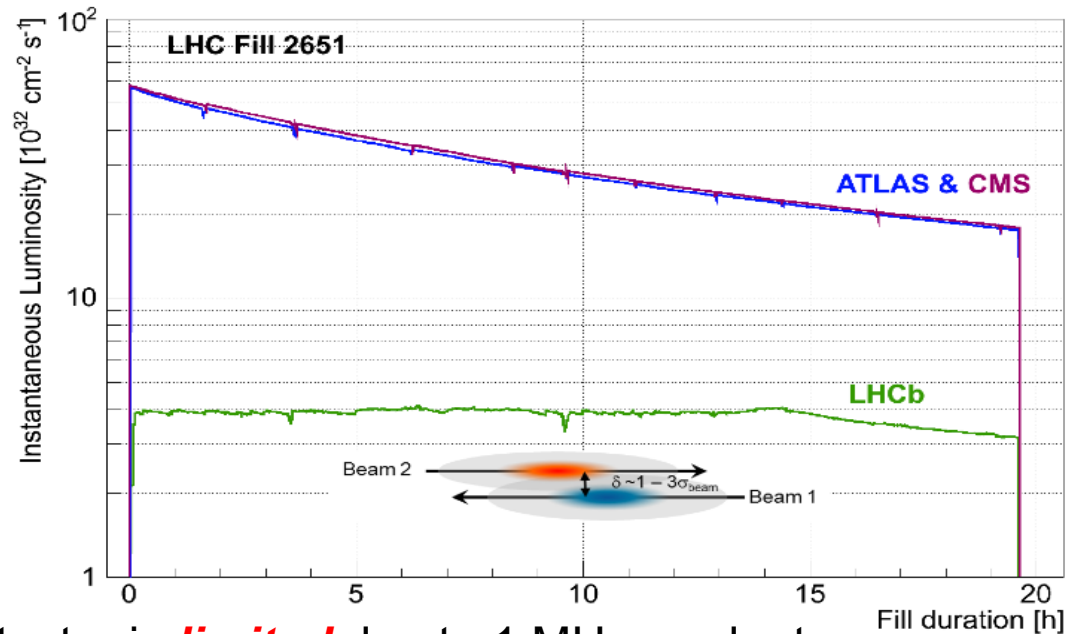
Separated from primary vacuum by thin **RF foil** with complex shape  
– Protection from beam pickup



**Moves away** every fill and **centers around the beam** with self measured vertices

# Why upgrade LHCb – Phase 1 (LS2)

- Currently LHCb can cope with a inst. lumi. higher than design
  - LHC still provides more than what we can handle:



- **Current** detector is **limited** due to 1 MHz readout.
- Higher Luminosities do not translate to higher physics: need smart Trigger.
- The upgrade is planned as a major Trigger/Readout upgrade:
  - From 1 to **40 MHz** full readout → Every collision read out to a computing farm
  - Higher instantaneous Luminosity → Higher occupancies/**Faster Ageing**
  - Change all the front-end!

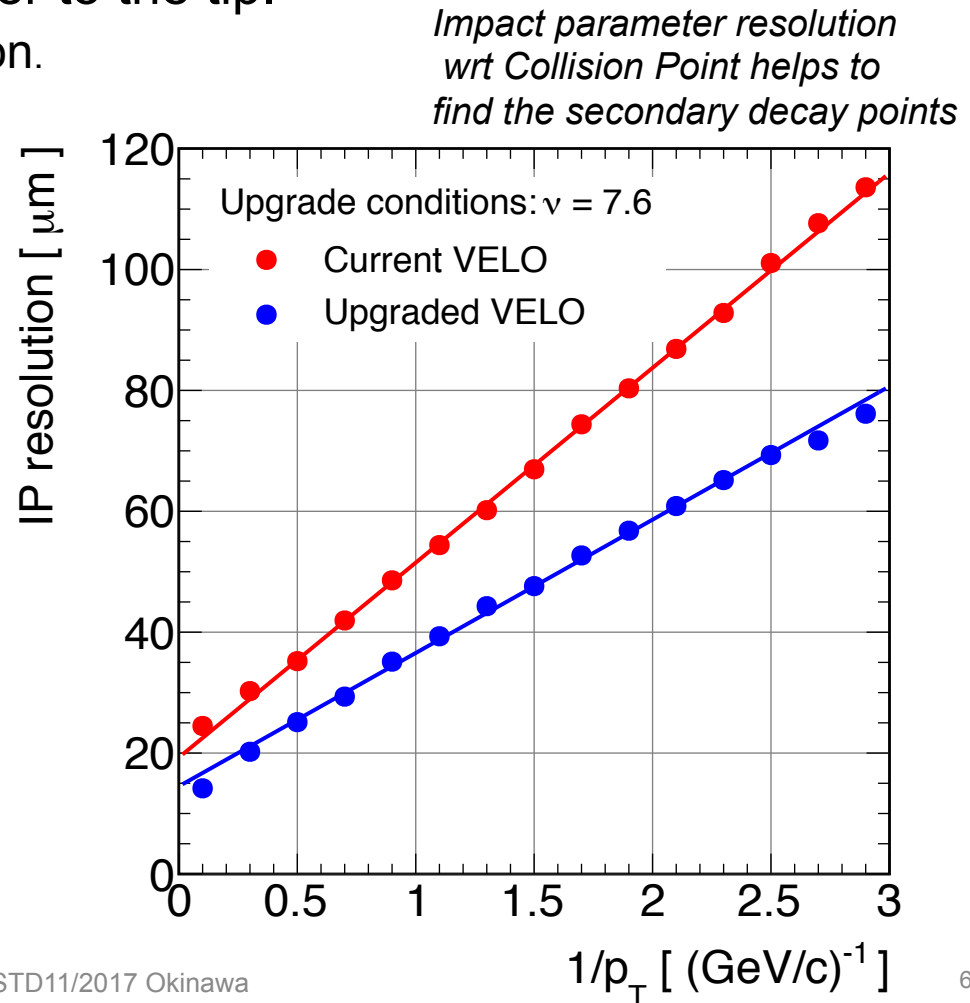
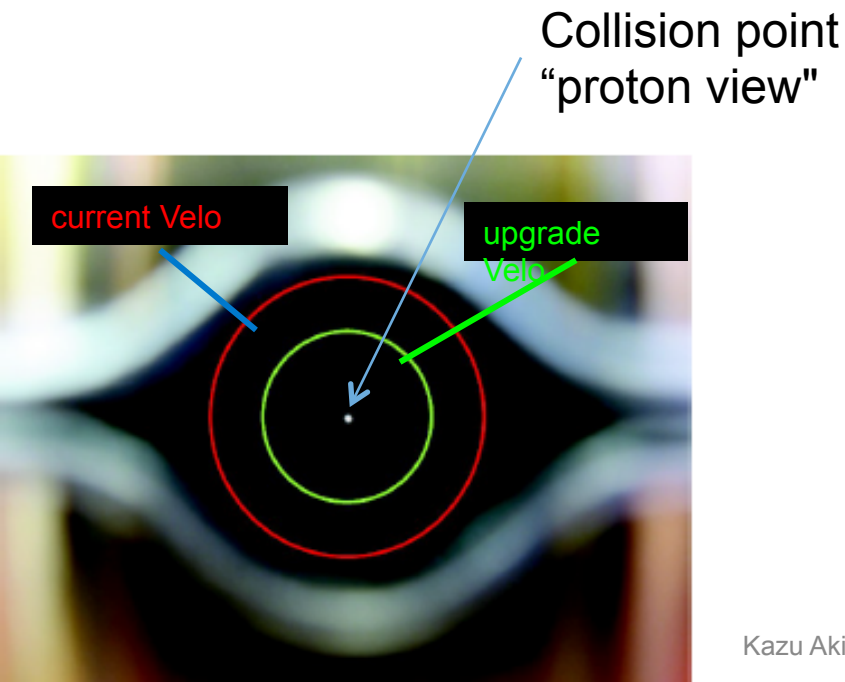


# Main challenges for the Velo Upgrade

Non uniform <u>Radiation</u> exposure	$8 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$ @ tip close to IP, $\sim 0.1 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$ @ outer edge
Sensor <u>HV</u> tolerance	1000V after $50 \text{ fb}^{-1}$
Readout data <u>rate</u>	$\sim 33 \text{ tracks/Event/module.}$ (LHC: $40 \text{ MHz}/25 \text{ ns}$ )
Low <u>Temperature</u> operation	$-20 \text{ C}$ @ tip close to the beam
<u>ASIC</u> power consumption	3W/ASIC; up to 36 W/module;
<u>Material</u> budget	Good IP and tracking resolution currently: <ul style="list-style-type: none"><li>• Proper time resolution <math>\sim 50 \text{ fs}</math></li><li>• IP resolution <math>\sim 40 \text{ mm}</math> (<math>p_T=1 \text{ GeV}</math>)</li></ul>

# Changes to improve: Closer, lighter, more segmented

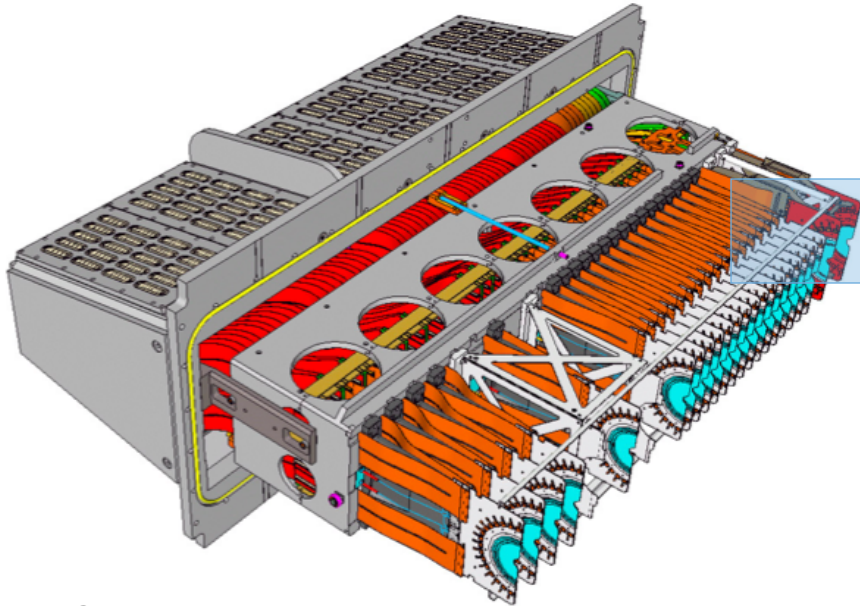
- From strips to pixels:  **$55 \times 55 \mu\text{m}^2$**  pixel.
  - Fast and robust pattern recognition. – better signal to noise
- Cooling interface needs to come closer to the tip.
  - Plan to use  $\mu$ -channels etched in silicon.
- First active element at  **$5.1 \text{ mm}$  from beam** (was  $8.2 \text{ mm}$ )
- New RF-foil required.





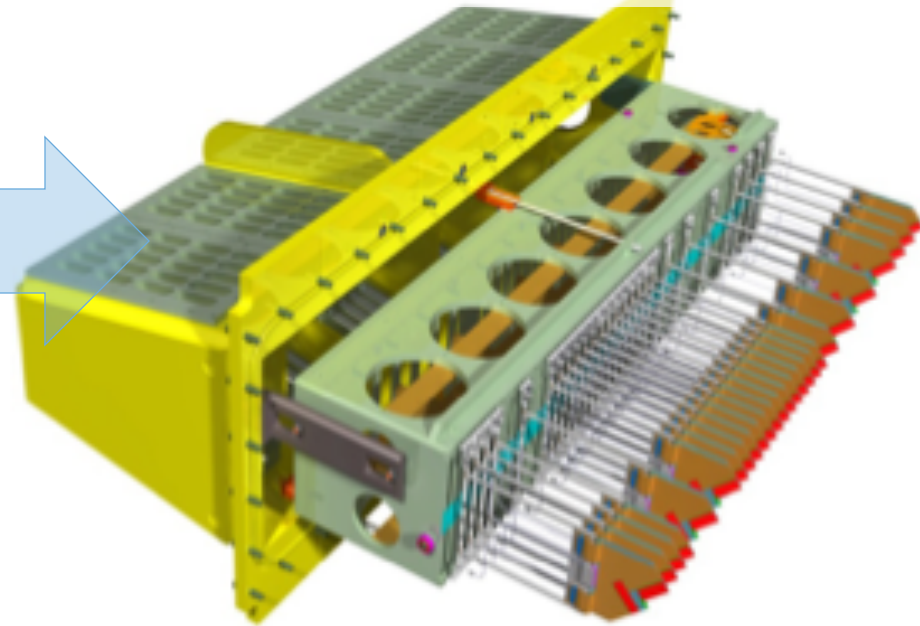
# Upgrade Plan

Current detector Half



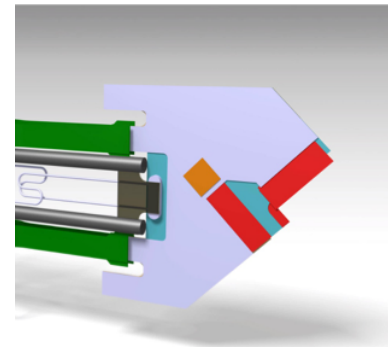
44 C shaped double sided modules (R/ $\phi$ )  
→ 88 sensors.

Upgrade detector Half

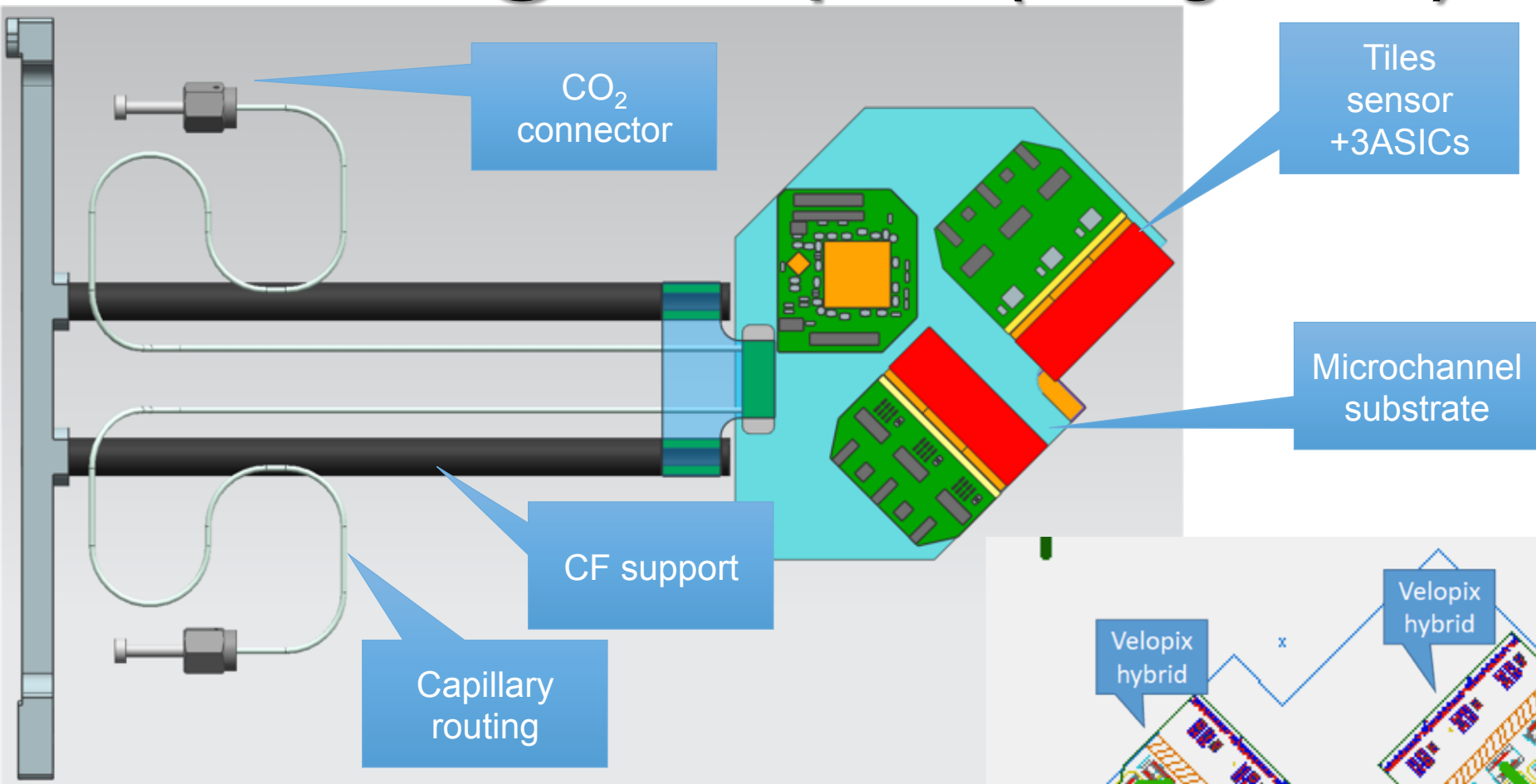


52 L (K) shaped pixel modules  
→ 208 sensors.

**Keep vacuum and motion features.**

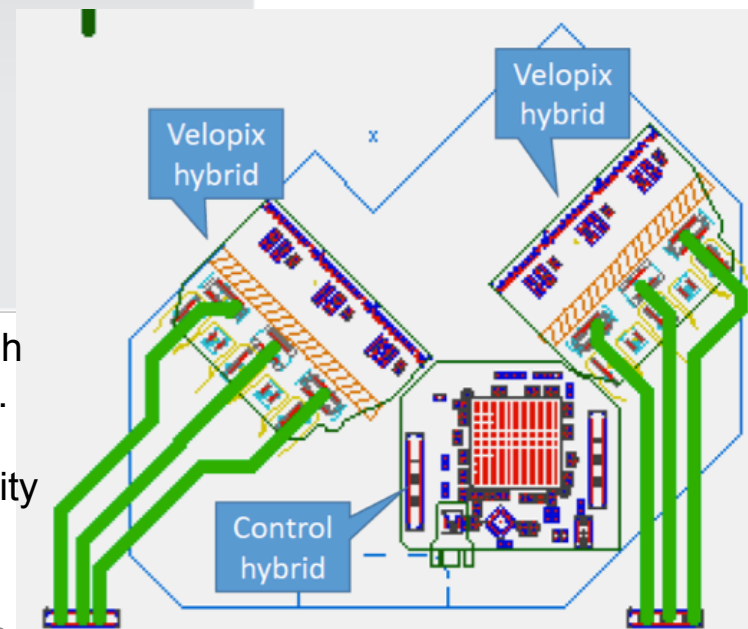


# Modules: 52 @ 25mm pitch (along beam)



Substrate should provide efficient and stable cooling, withstand high pressures, be radiation hard with low outgassing, and be planar i.e. suitable for gluing and wire bonding

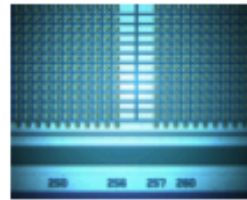
The physics performance requires low mass and mechanical stability



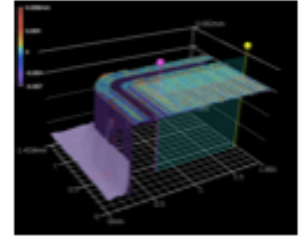


# Silicon sensors

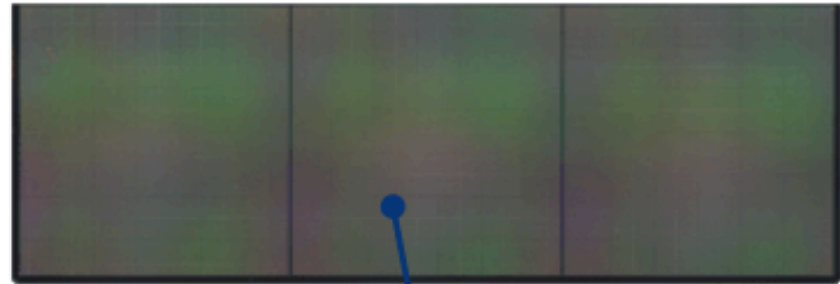
- n-in-p
- Tile for 3 ASIC chips
- 200  $\mu\text{m}$  thick
- 55x55  $\mu\text{m}^2$  pixels
- Non uniform irradiation ( $\sim r^{-2.1}$ )
- Tip close to beam:  $8 \times 10^{15} n_{\text{eq}}$ ,  
far corner only at  $0.8 \times 10^{14} n_{\text{eq}}$
- guard ring width  $\sim 450 \mu\text{m}$
- Bias of 1000V after 50 fb $^{-1}$



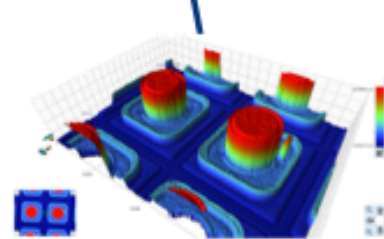
elongated pixels  
between ASICs



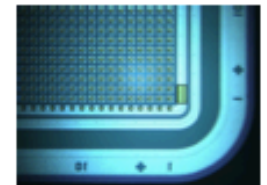
Sensor Thickness  
200  $\mu\text{m}$



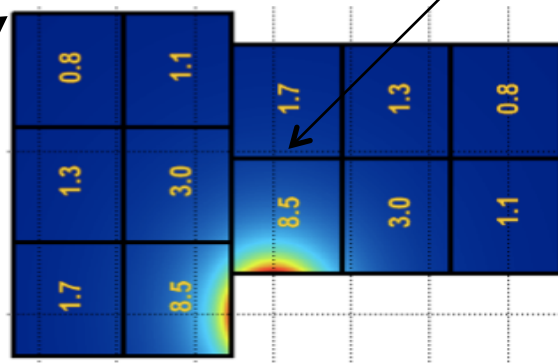
silicon



sensor UBM pads



rounded,  
DRIE etched  
corners



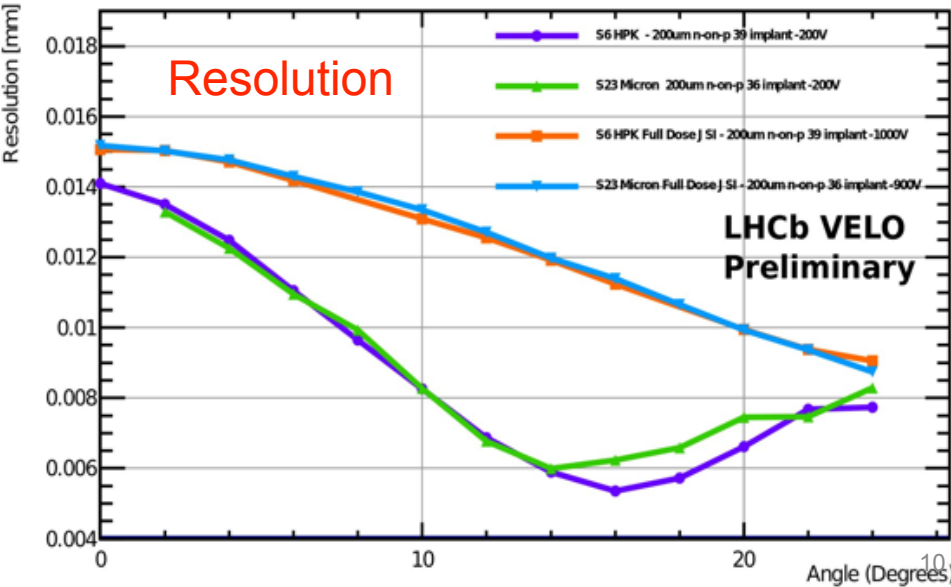
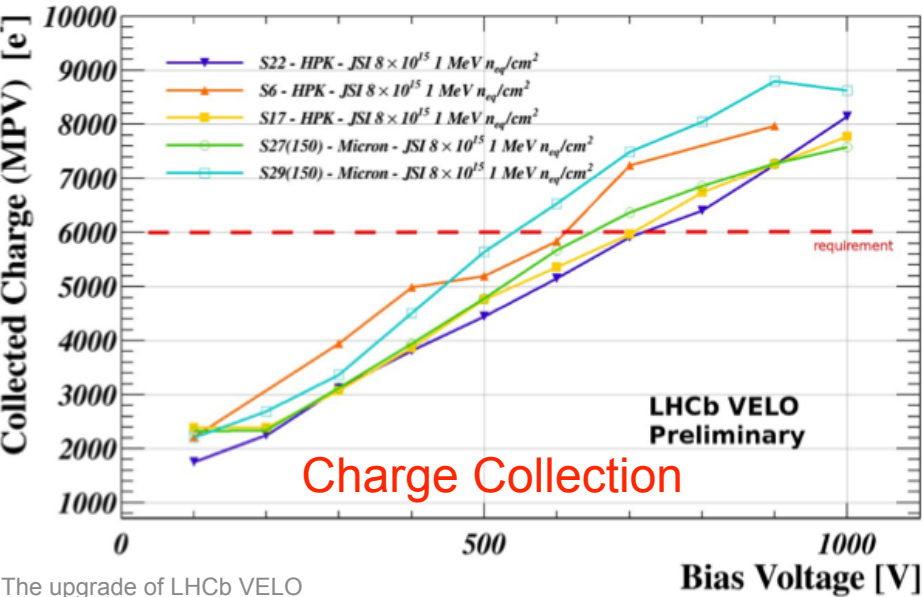
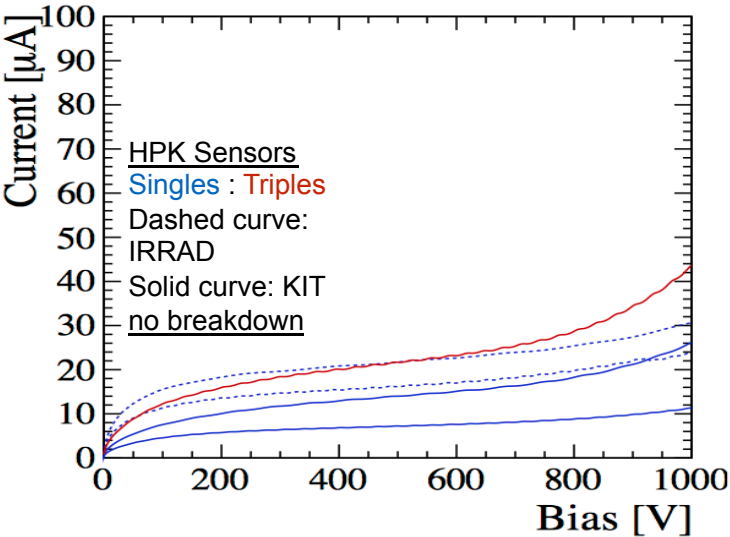
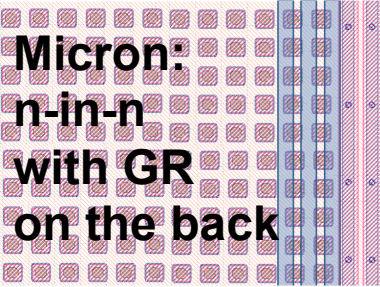
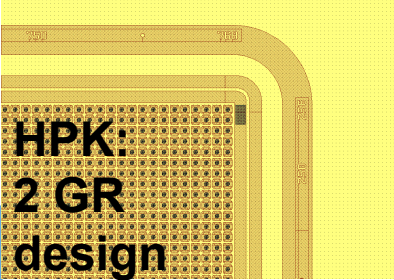
factor 1/7

factor 1/20

factor 1/100

# Sensor: Prototyping

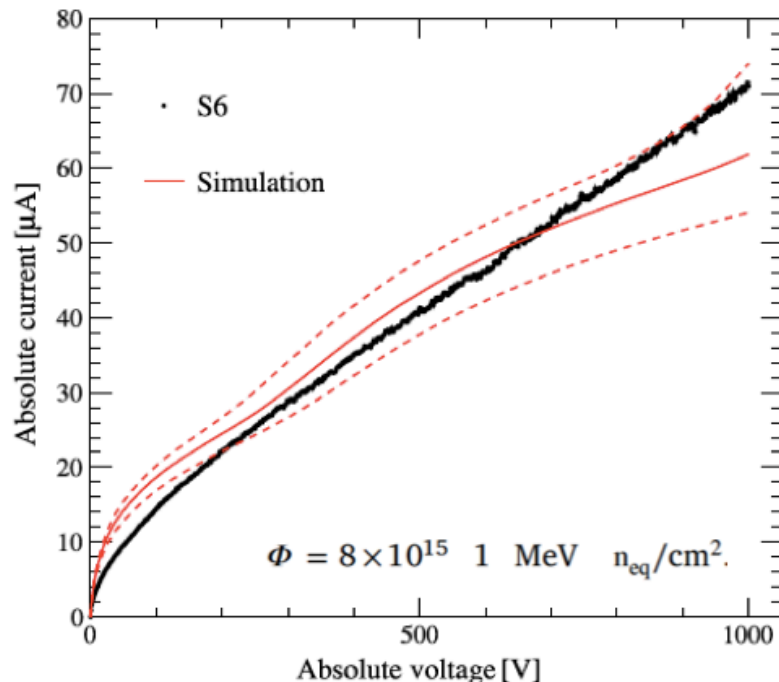
	Micron n-on-n	Micron n-on-p	Hamamatsu n-on-p
Thickness	150 $\mu\text{m}$	200 $\mu\text{m}$	200 $\mu\text{m}$
Implant size	36 $\mu\text{m}$	36 $\mu\text{m}$	39 $\mu\text{m}$ 35 $\mu\text{m}$
Guard ring pixel to edge	450, 250, 150 $\mu\text{m}$	450, 250, 150 $\mu\text{m}$	450, 600 $\mu\text{m}$



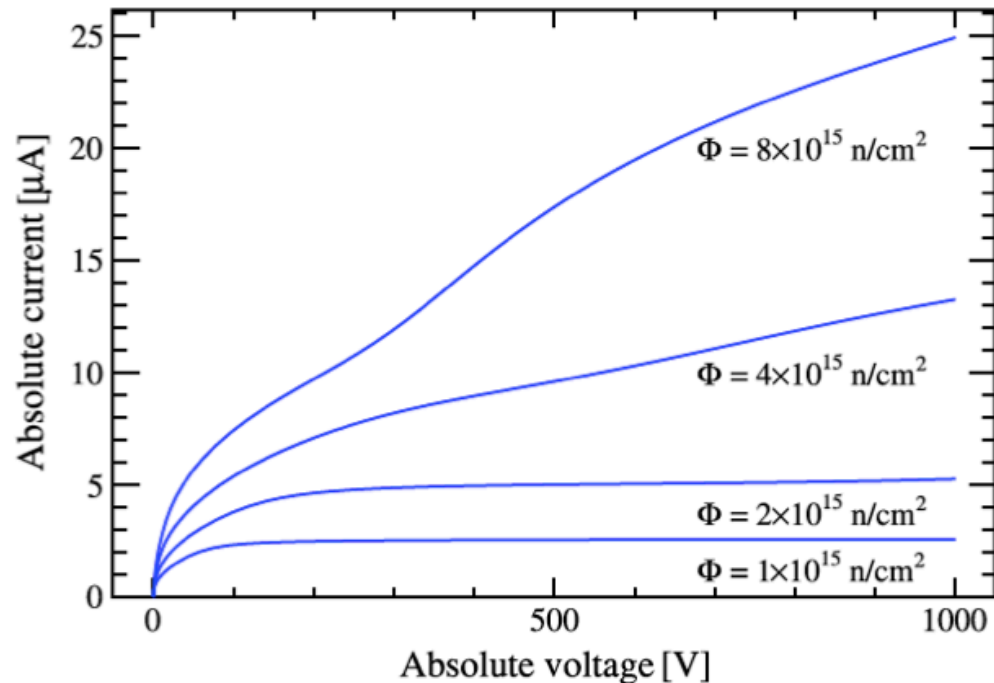


# Current model for irradiated sensors

- **need a model**
  - valid for our irradiation range
  - capable of describing the changing IV curves we see
  - focus on bulk effects
- **Folkestad-LHCb model:**
  - *Nucl. Inst. and Meth. A 874 (2017) p94-102*



(a)  $T = -31.8^\circ\text{C}$ .

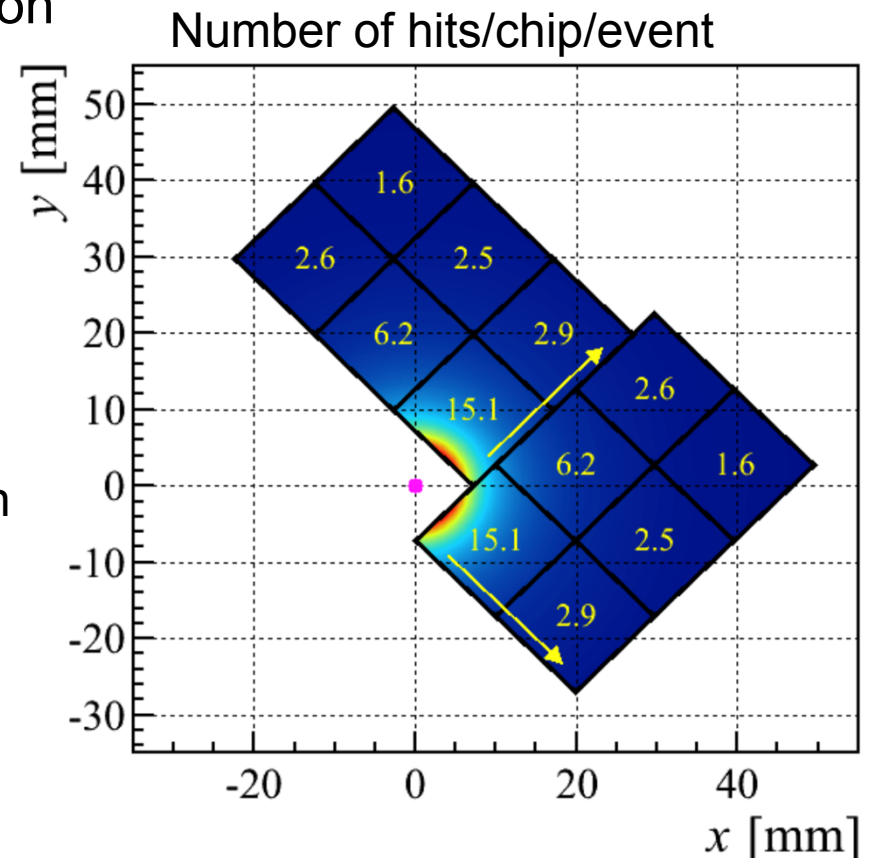


- inspired by Perugia and EVL models
- contains one donor level, one shallow and one deep acceptor
- TCAD simulations show Reasonable agreement with data

Linear Increase  
in current for heavily  
Irradiated substrates  
Due to avalanche

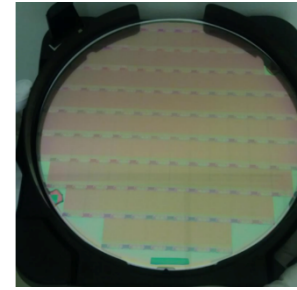
# ASIC Challenges

- Average # particles / chip / event
  - average (peak) rate: multiply by 26.8 (40) MHz
- Hottest chip → 230 (320) Mtracks/s ~ 600 (900) Mhits/s per chip
  - grouping of pixel hits
  - 2x4 super pixels → 30 % data reduction
- Output bandwidth of (hottest) VeloPix:
  - Average: 13 Gbit/s ; peak: 20 Gbit/s
  - 4 links at ~ 5 Gbit/s
- High radiation environment:
  - SEU protection: triple redundancy
  - Extensive tests with heavy Ion irradiation



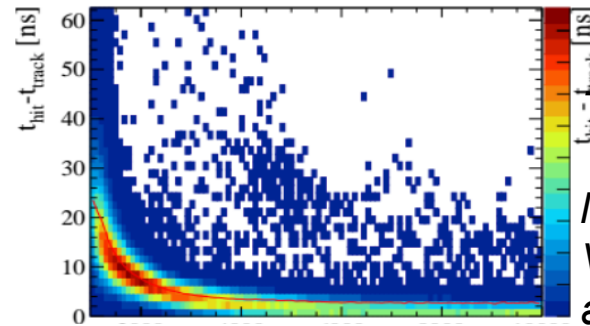


# VeloPix ASIC



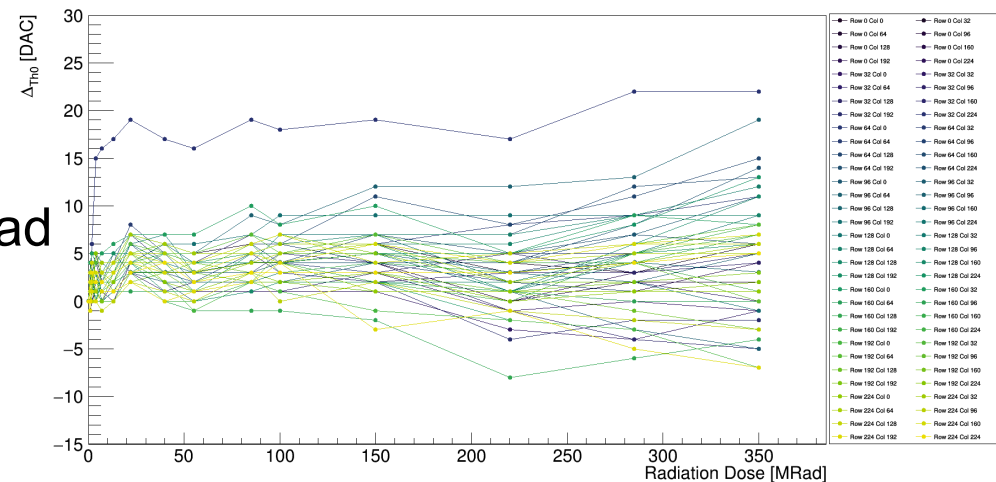
*VeloPix  
Wafer:  
Probe test  
station ready*

- Key features
  - Data driven readout: Each hit **time-stamped**, sent off chip immediately
  - Fast front-end: **time walk** < 25 ns
  - Binary readout – but optional Amplitude (slow) for calibration
  - Technology (130 nm TSMC)



*Time walk measured with Timepix3: lower signals are slower. VeloPix has a very similar analog design*

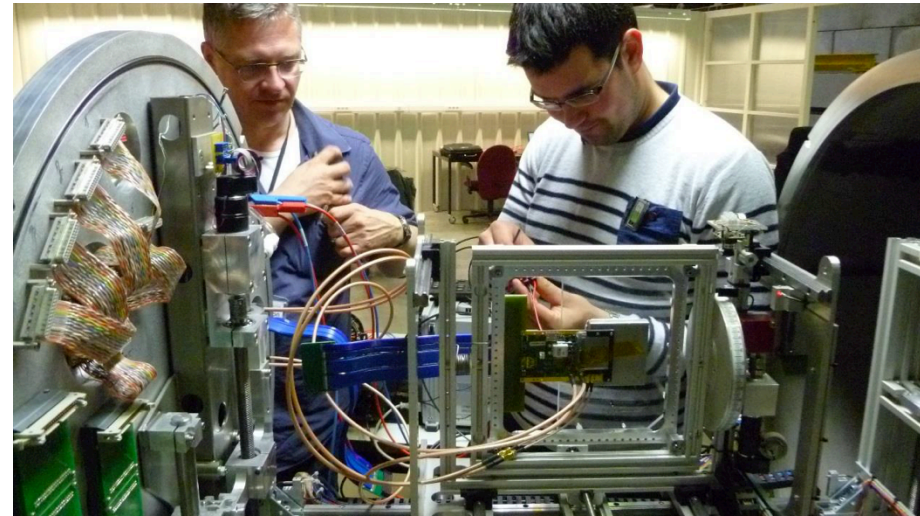
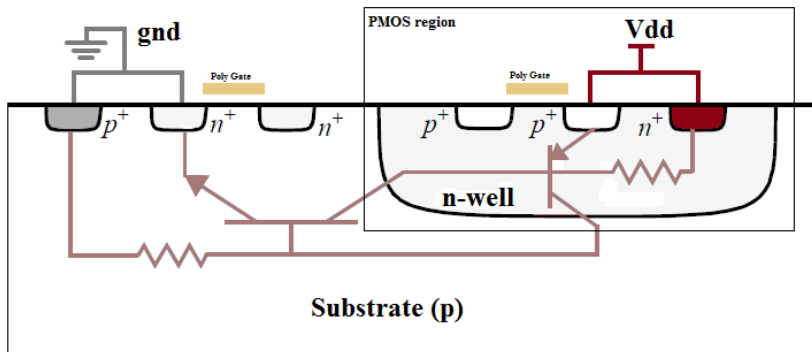
- Chips will be **thinned** to 200  $\mu\text{m}$ :  
→ minimize material
- Test done with X-ray up to 400 MRad
  - No change in digital power consumption
  - No drift in analogue parameters: pixel thresholds, noise and global DACs remain stable



*threshold shift w.r.t. 0 Mrad*

# Single Event Upset Testing

- determine rate of single event upsets (bit-flips)
- Shoot heavy ions of various type / angles
  - Using heavy ion facility in Louvain-la-Neuve
- Found some issues – VeloPix v1:
  - Single Event Latch-up (SEL): a (local) short circuit on the power lines
  - And large x-sec for the reset circuit

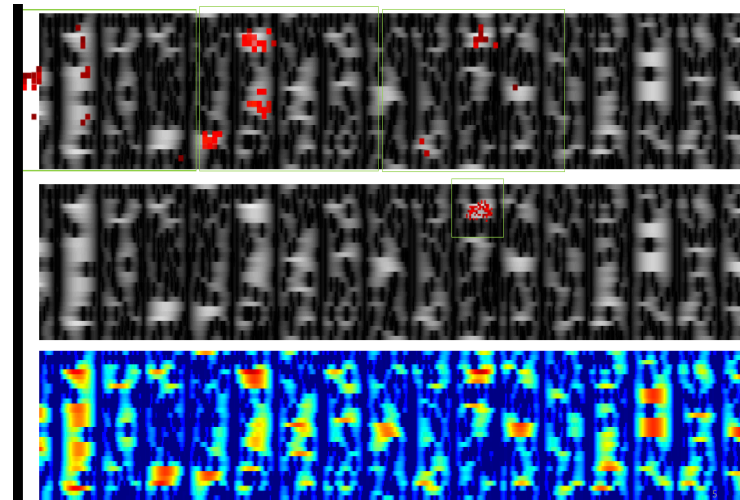
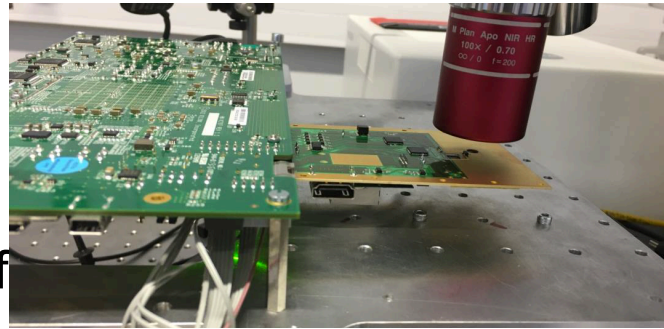


- SEL occurs in the matrix only
- strongly temperature dependent, not observed below -10 °C
  - though might still occur if tested for longer time
- SEL is due to higher substrate/well resistance in TSMC process.
- Solution: add extra substrate contacts to reduce distance to contact



# Laser testing

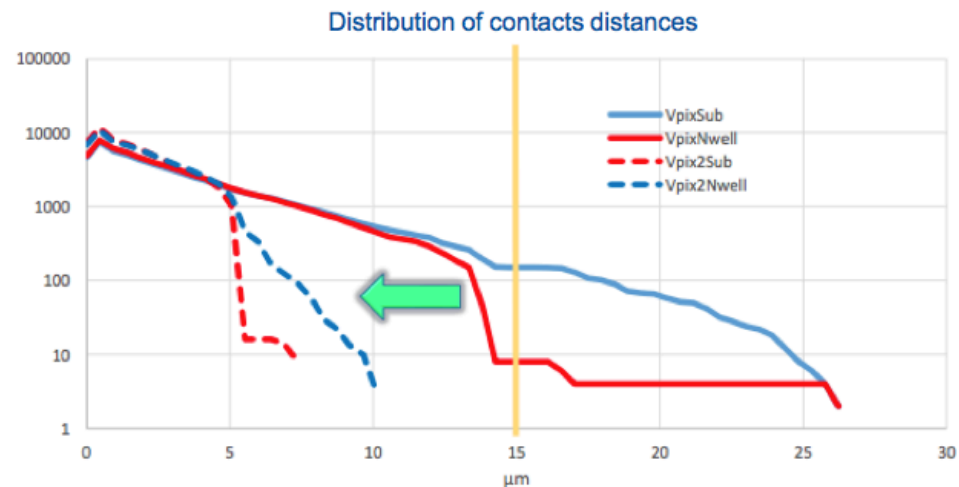
- SEL confirmed by injection of laser light at Montpellier facility
  - very precise position of charge injection
  - but can not scan whole chip, too many steps (1 or 3  $\mu\text{m}$  step size)
- NIR photons shot into chip from back side
- Local charge injection (also in depth) possible by two photon absorption
- VeloPix2 has these change already implemented.



observed  
SEL  
3  $\mu\text{m}$  steps

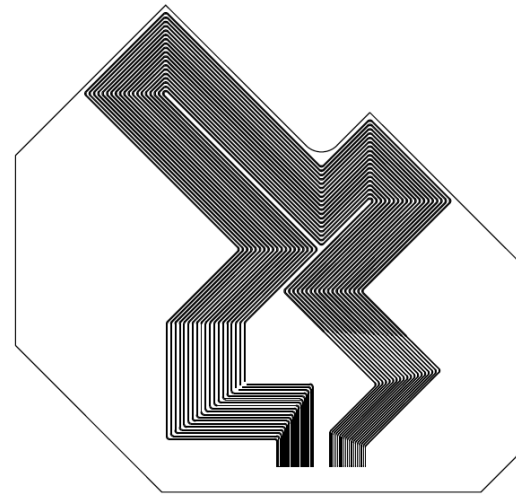
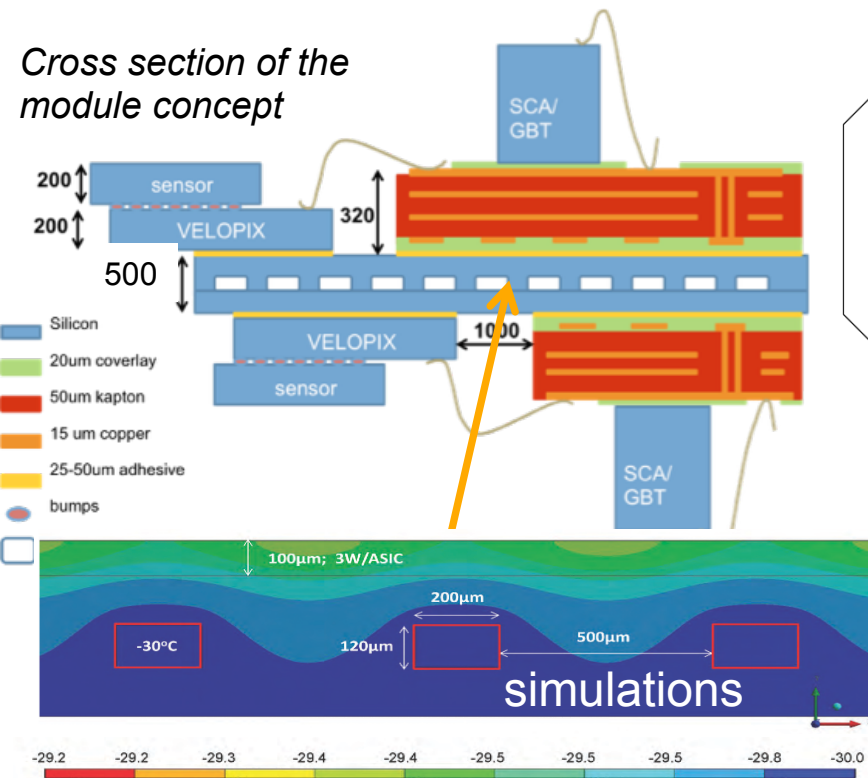
observed  
SEL  
1  $\mu\text{m}$  steps

design:  
distance  
to contact

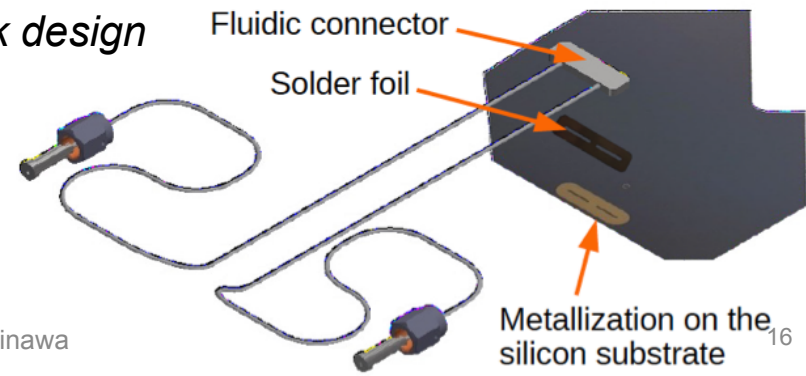
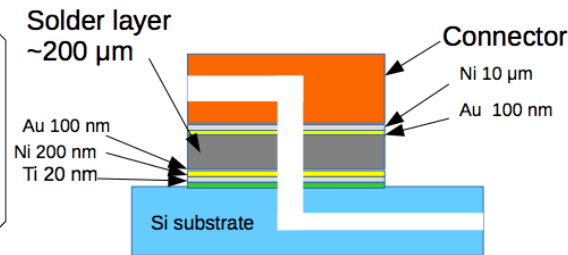


# Cooling: micro channel substrate

- Power consumption can go up to ~40W/module.
- Keep the sensors at  $< -20\text{ }^{\circ}\text{C}$  to minimize the effects of radiation damage, and avoid thermal runaway
- Novel method: evaporate  $\text{CO}_2$  via micro-channels etched in Si substrate → Same Thermal Expansion Coefficient (CTE)

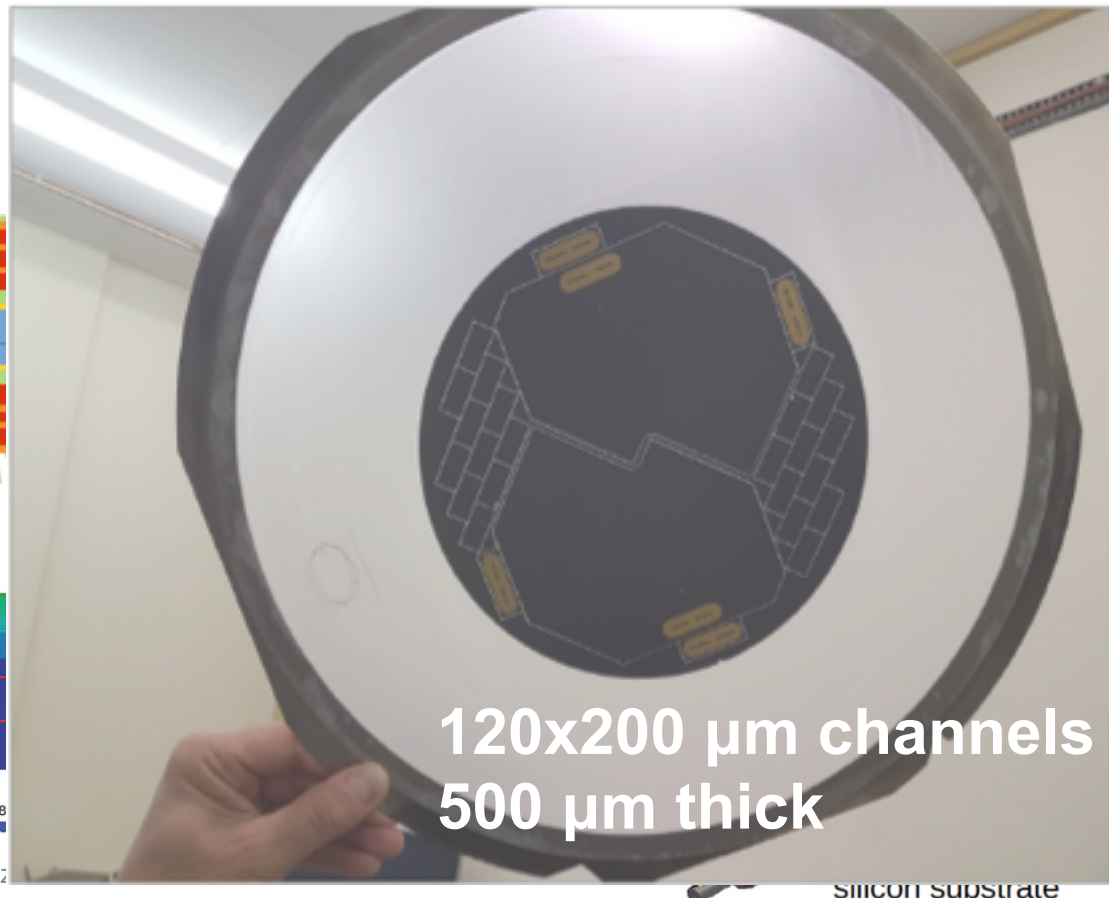
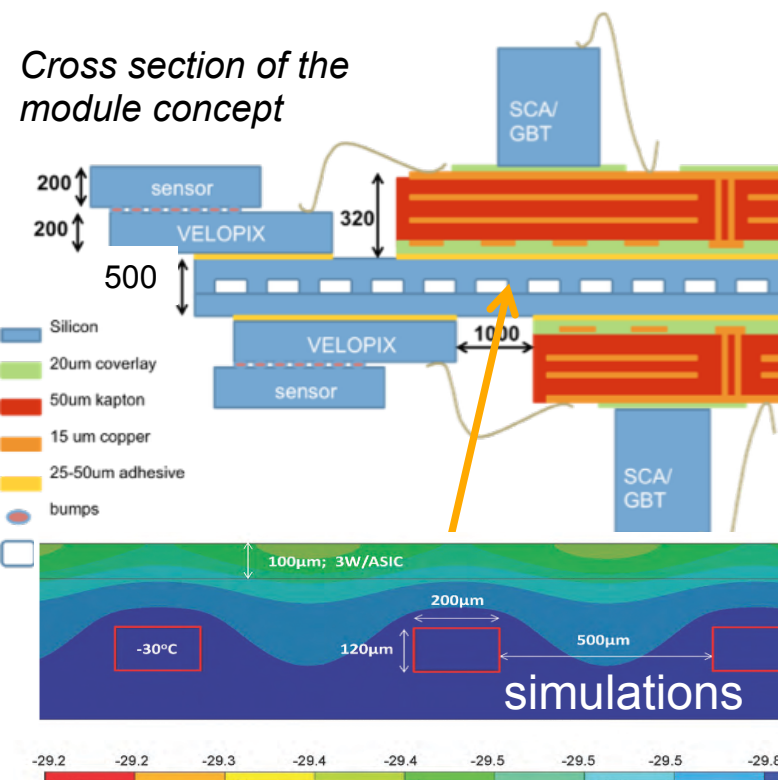


*Race track design*



# Cooling: micro channel substrate

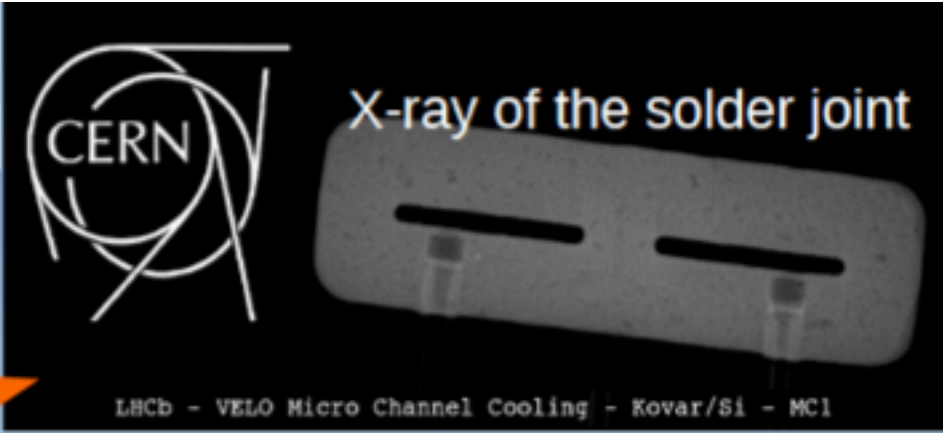
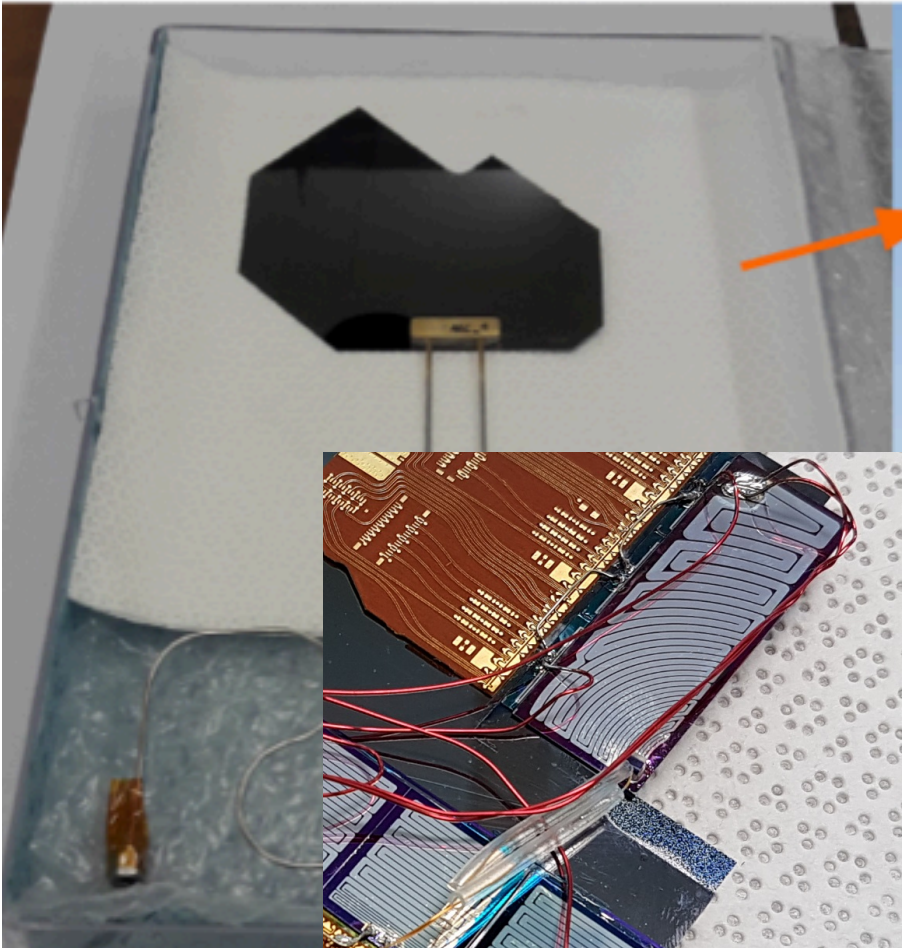
- Power consumption can go up to  $\sim 40\text{W}/\text{module}$ .
- Keep the sensors at  $< -20\text{ }^{\circ}\text{C}$  to minimize the effects of radiation damage, and avoid thermal runaway
- Novel method: evaporate  $\text{CO}_2$  via micro-channels etched in Si substrate  $\rightarrow$  Same Thermal Expansion Coefficient (CTE)





# Microchannel Performance

First microchannels soldered  
on September 1<sup>st</sup> 2017



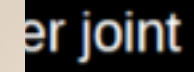
- Overhang sensor powered up to 1.3W
- Temperatures measured with PT100 probes
- In vacuum

Sensor Power (W)	dT (C) of Sensor tip
0	2.7
0.100	2.9
0.240	3.3
0.400	3.7
0.650	4.2
0.940	5.0
1.28	5.7

Realistic heaters glued with  
Araldite 2020, thin layer

All four tiles powered to 26W

First m  
on Sep



- MC1

probes

sor

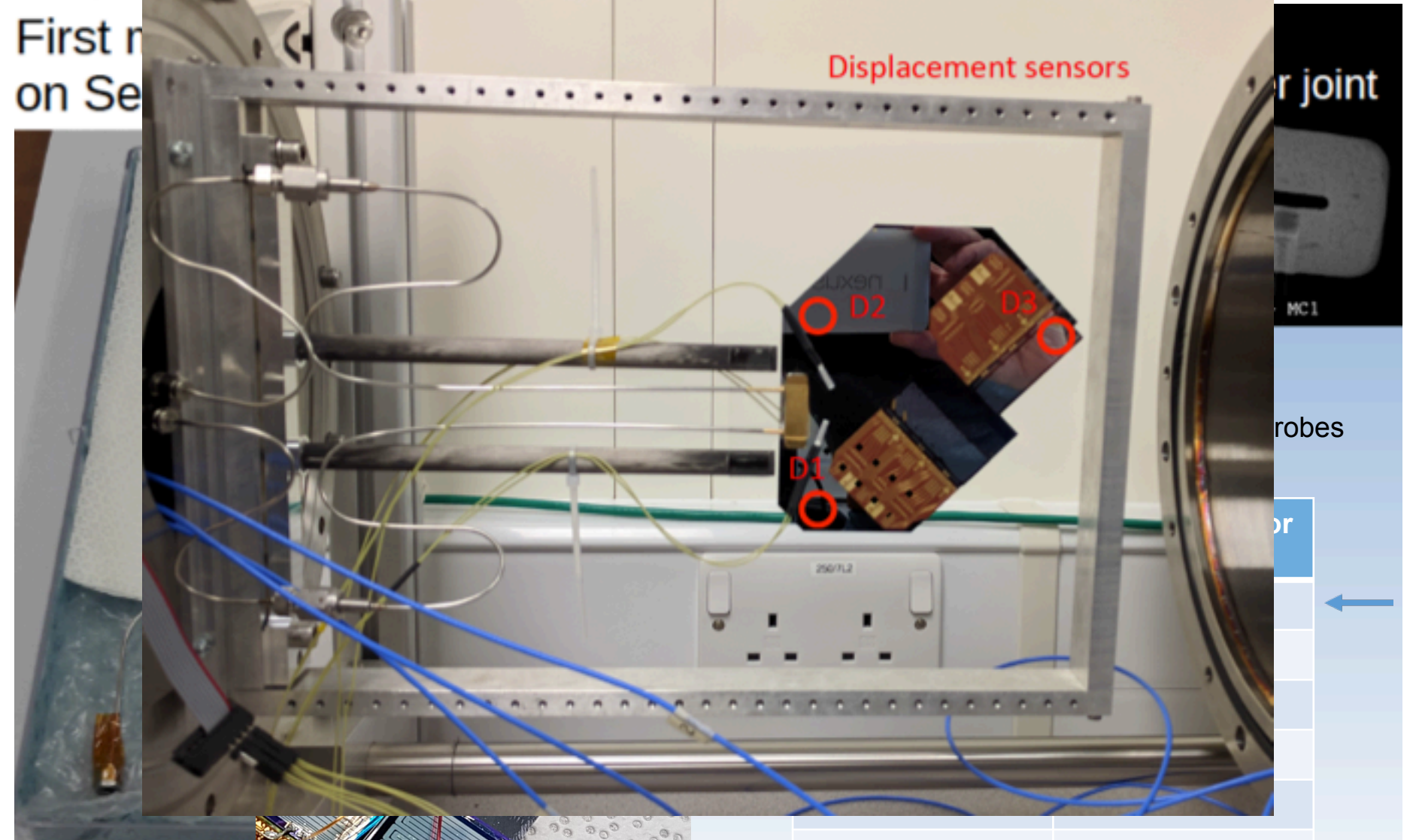


Realistic heaters glued with Araldite 2020, thin layer





# Microchannel Performance



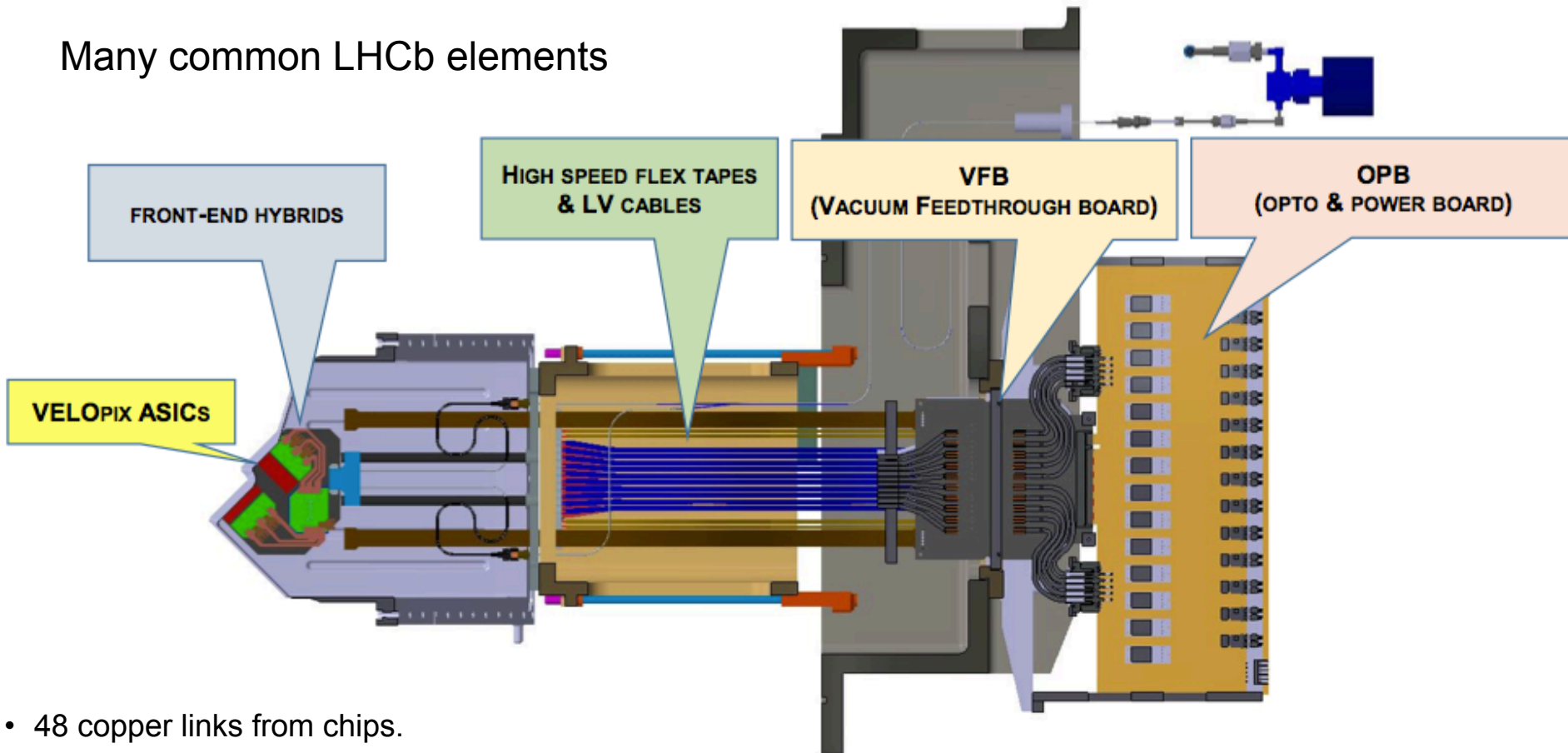
Realistic heaters glued with  
Araldite 2020, thin layer  
All four tiles powered to 26W

0.940	5.0
1.28	5.7



# Electronics chain: overview

Many common LHCb elements

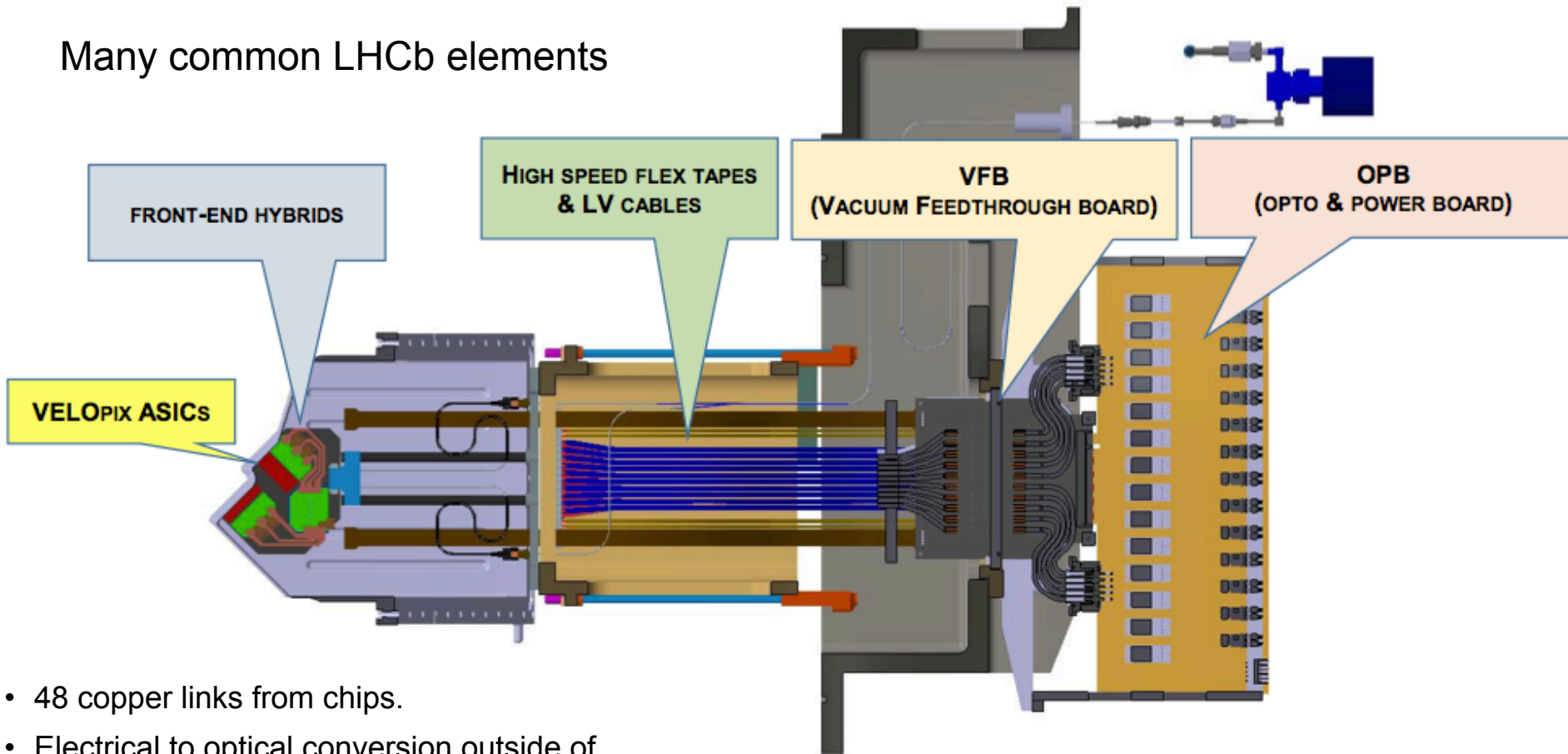


- 48 copper links from chips.
- Electrical to optical conversion outside of vacuum tank → 20 Optical links ~5 Gbit/s each
- 1 FPGA to reads out 1 module

VELO specific components involve:  
data transmission,  
backend data acquisition and  
Time reordering of hits/clusters.

# Electronics chain: overview

Many common LHCb elements



- 48 copper links from chips.
- Electrical to optical conversion outside of vacuum tank → 20 Optical links ~5 Gbit/s each
- 1 FPGA to reads out 1 module

**Prototypes of all components currently under test**

# Upgrade RF Foil

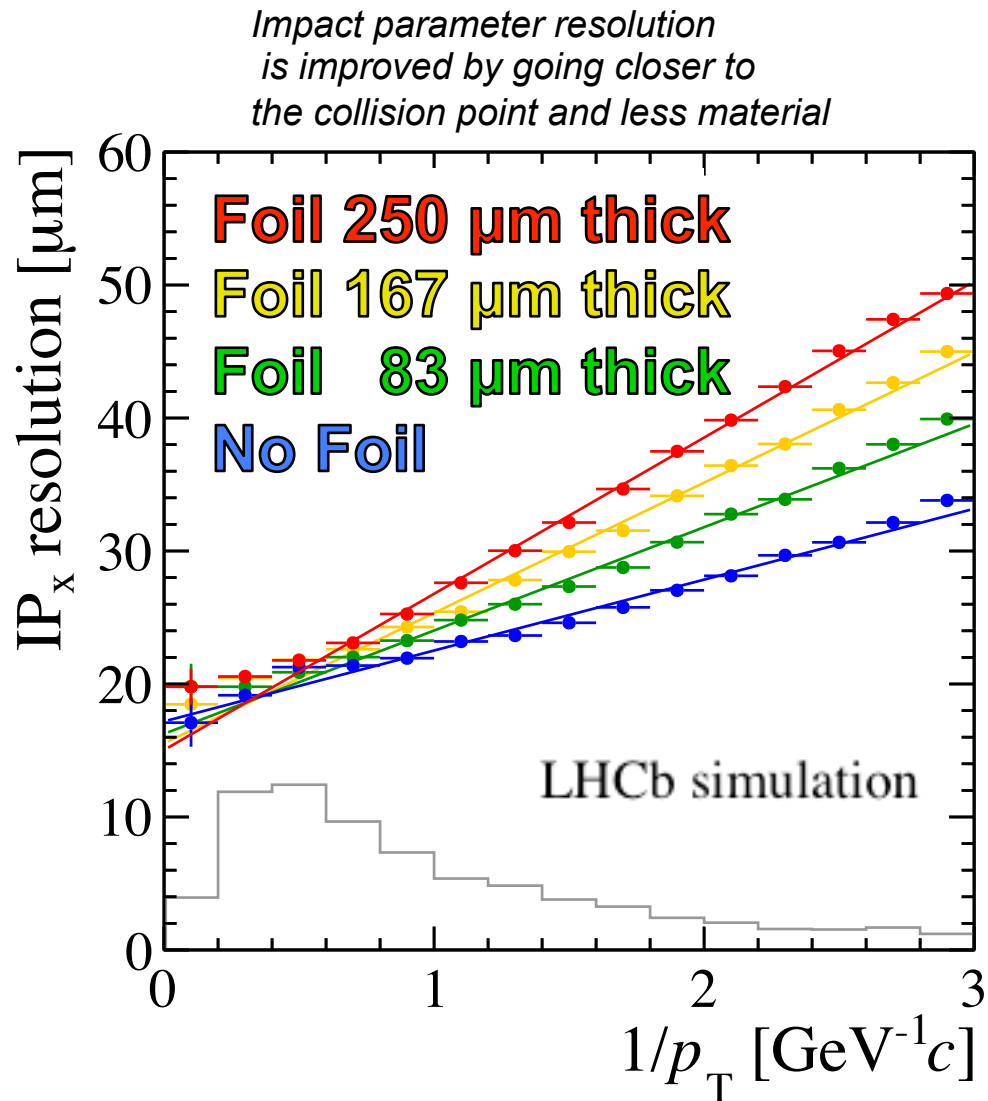
- Requirements

- Vacuum tight ( $< 10^{-9}$  mbar l/s)
- Radiation hard
- Low Mass
- Good electrical conductivity
- Thermally stable and conductive

- Material and fabrication:

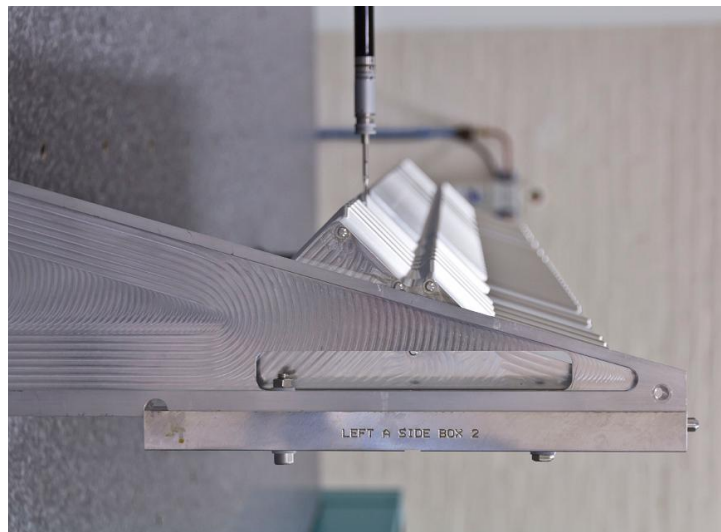
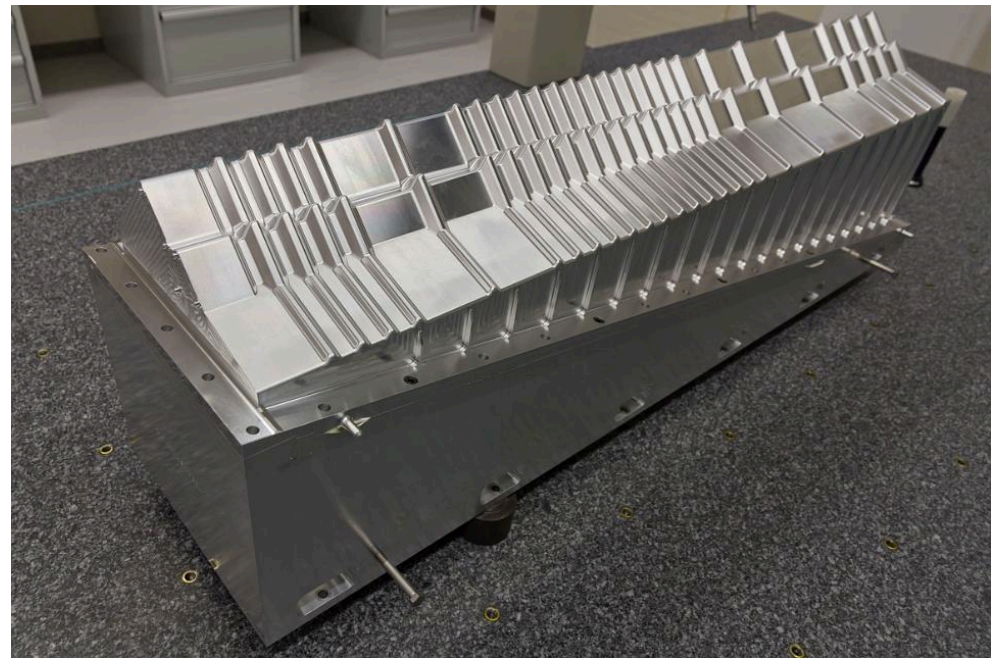
- Aluminium (AlMgMn).
- **500  $\mu\text{m}$  thickness**:
- By 5-axis milling of a single homogeneous block

- Chemical etching – 250 $\mu\text{m}$



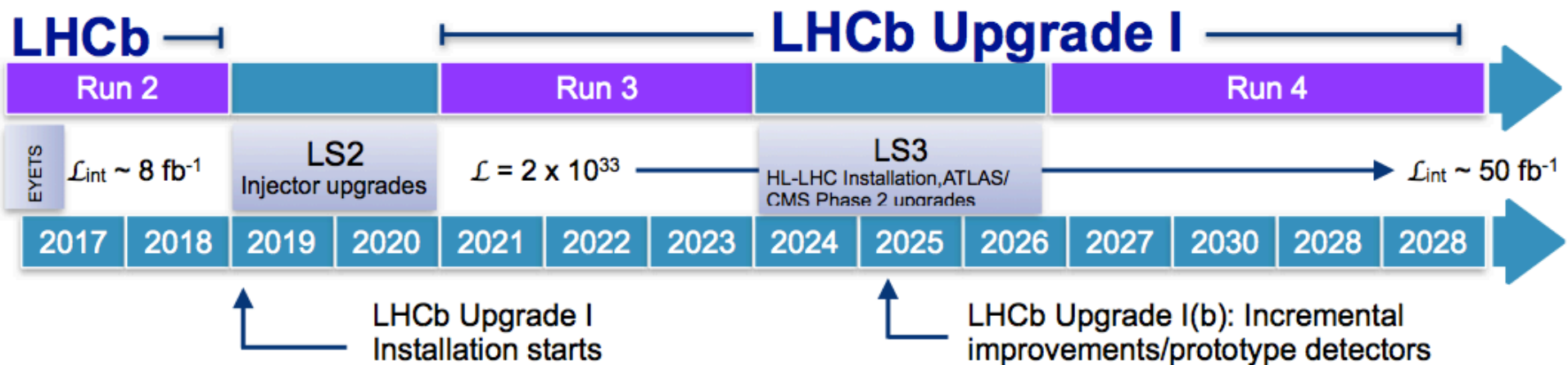


# Upgrade RF Foil Prototypes



- TL: start with an Al Block.
- BL: milling machine
- TR Full size foil with  $500\ \mu\text{m}$
- BR: metrology of prototype

# Timeline



Many Engineering Design Reviews (EDR) done in 2017  
 Some parts already gone through Production Readiness Review (PRR)

# Summary

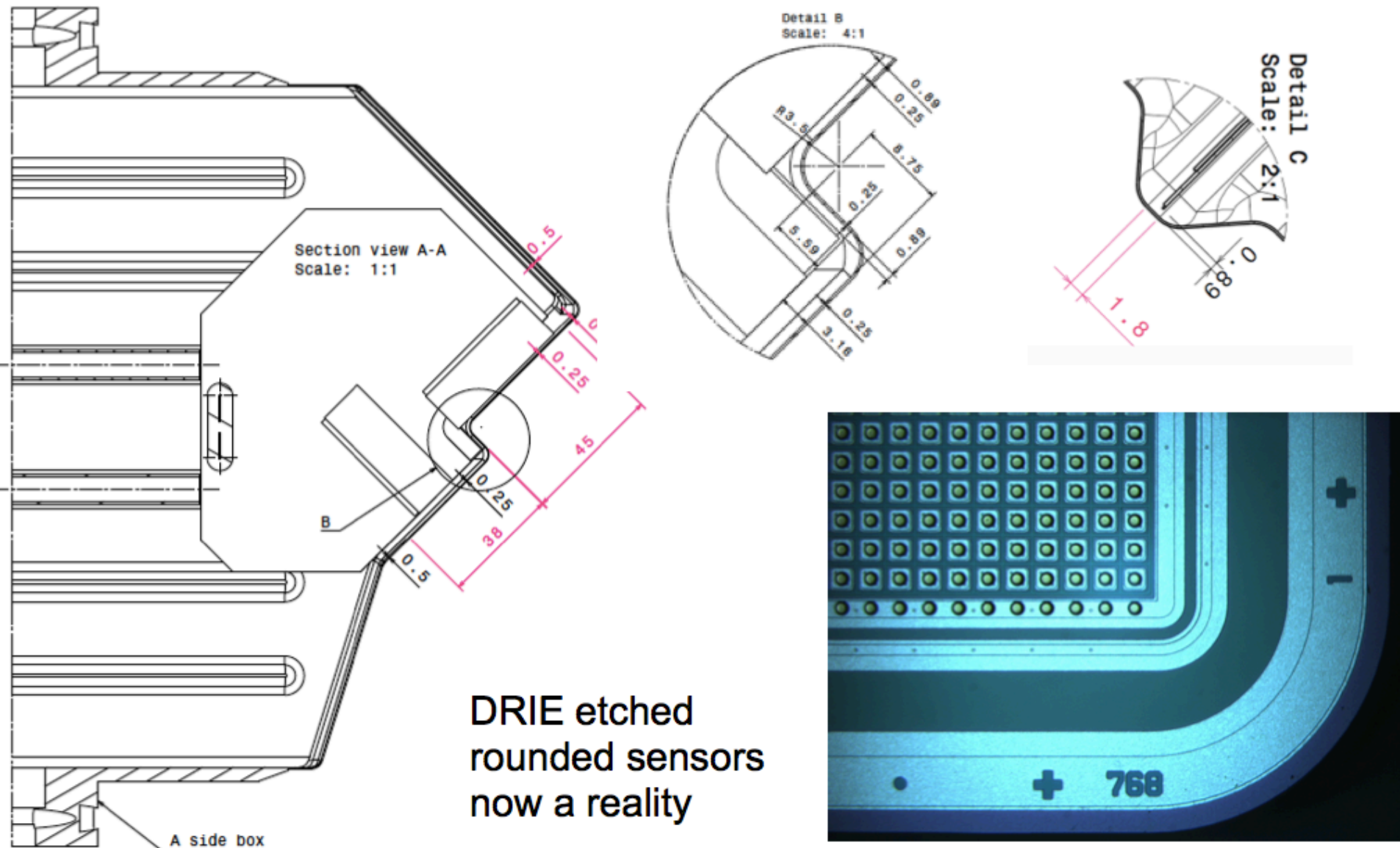
- We plan to install a fully upgraded detector in the **LS2/2019**
- With a 40 MHz “**triggerless**” readout
- Run @  $L = 2 \times 10^{33} \text{ cm}^{-2} \text{ s}^{-1}$  (5x now), but front-end **40 times higher rate**.
- VELO subdetector will consist planar silicon pixel sensors with  $55 \times 55 \mu\text{m}^2$  pitch
  - Get closer to the collision point
  - Bigger segmentation
- New ASIC VeloPix with 20 Gbit/s output bandwidth
- Evaporative  $\text{CO}_2$  cooling in Silicon with a **micro-channel** substrate as interface
- 500/250  $\mu\text{m}$  thick RF-box milled from solid block of Aluminum
- Developments for the upgrade going well and on schedule

**The LHCb VELO upgrade is a challenging project with many new techniques**

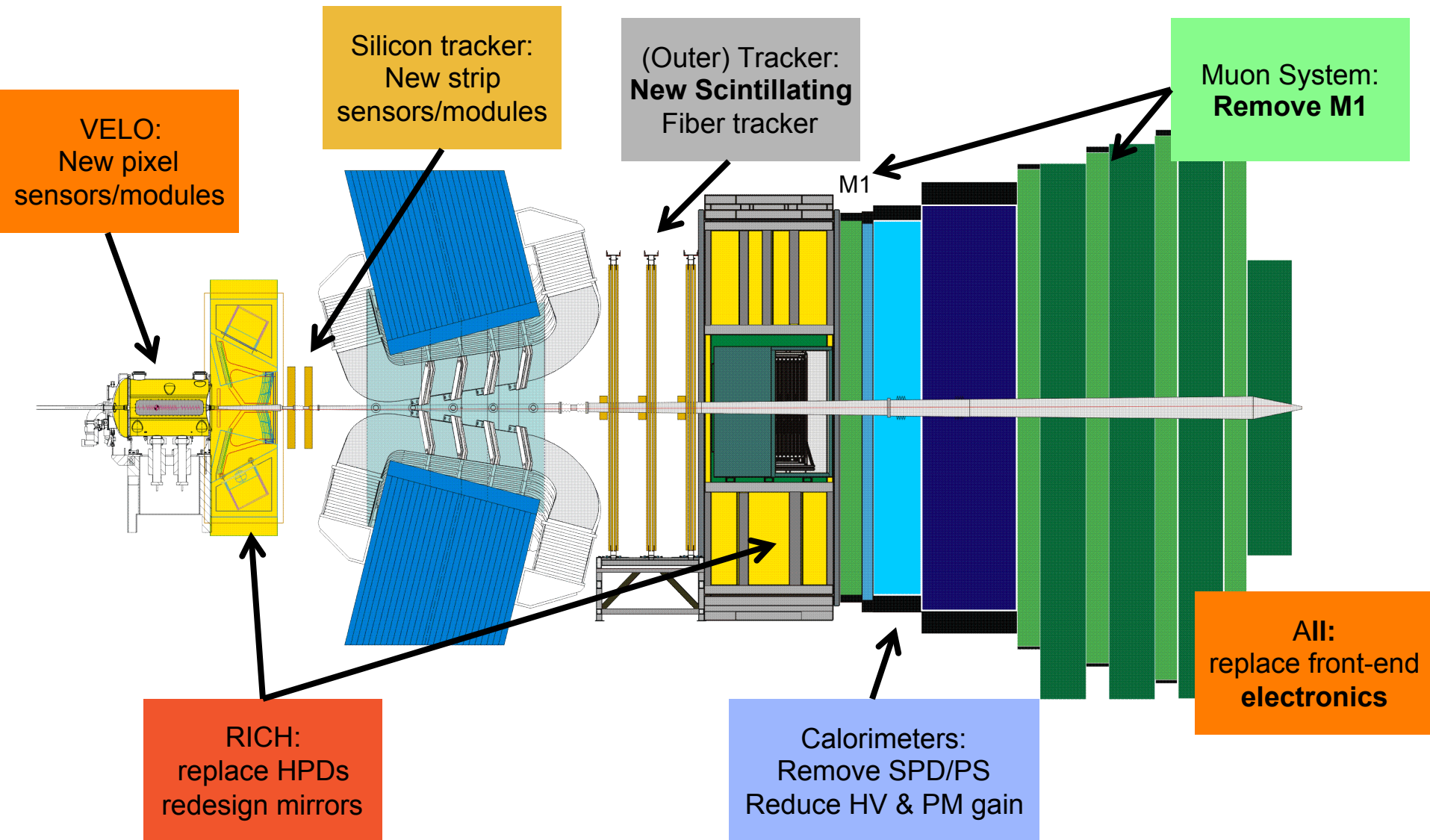


Back up

# Foil clearances and dedicated sensors



# LHCb Upgrade Overview



# VeloPix ASIC

Specification	Timepix3	VeloPix
pixel dimension	55x55 $\mu\text{m}^2$	55x55 $\mu\text{m}^2$
matrix size	256x256	256x256
timewalk	< 25 ns	< 25 ns
Time over Threshold range	10 bit	4 bit
leakage current compensation (per pixel)	> 20 nA	> 20 nA
Time stamp resolution	1.6 ns	25 ns
Time stamp range	18 bit	12 bit
sustainable hit rate	40 MHits/s	> 600 MHits/s
output bandwidth	2.5 Gbit/s	> 13.6 Gbit/s
power consumption per chip	< 2 Watts	< 3 Watts
radiation hardness	no spec.	> 400 MRad
single event upset robust	no	yes



# Silicon sensors

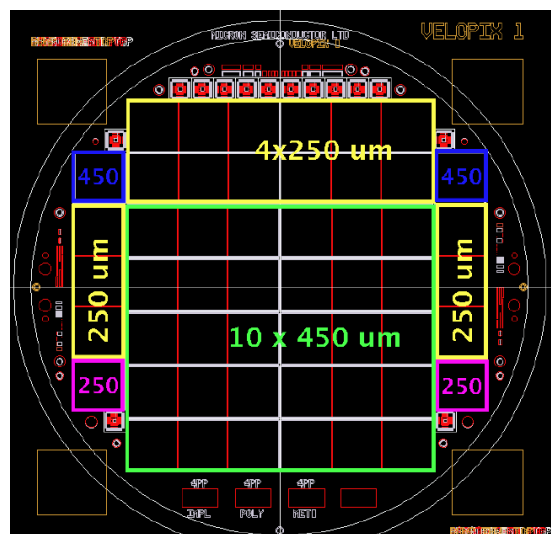
- Focus on two vendors with proven track record in radiation hard and HV tolerant sensor designs:

HPK



- n-in-p, 200 um thick
- 450 um guard ring
- 3x1 and single-ASIC sensors

Micron

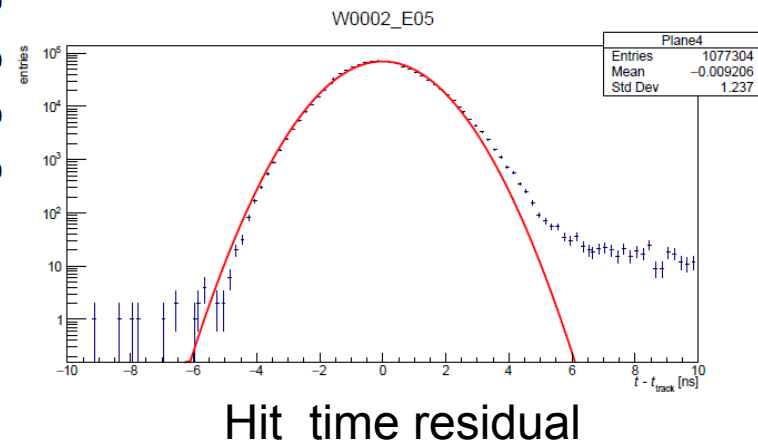
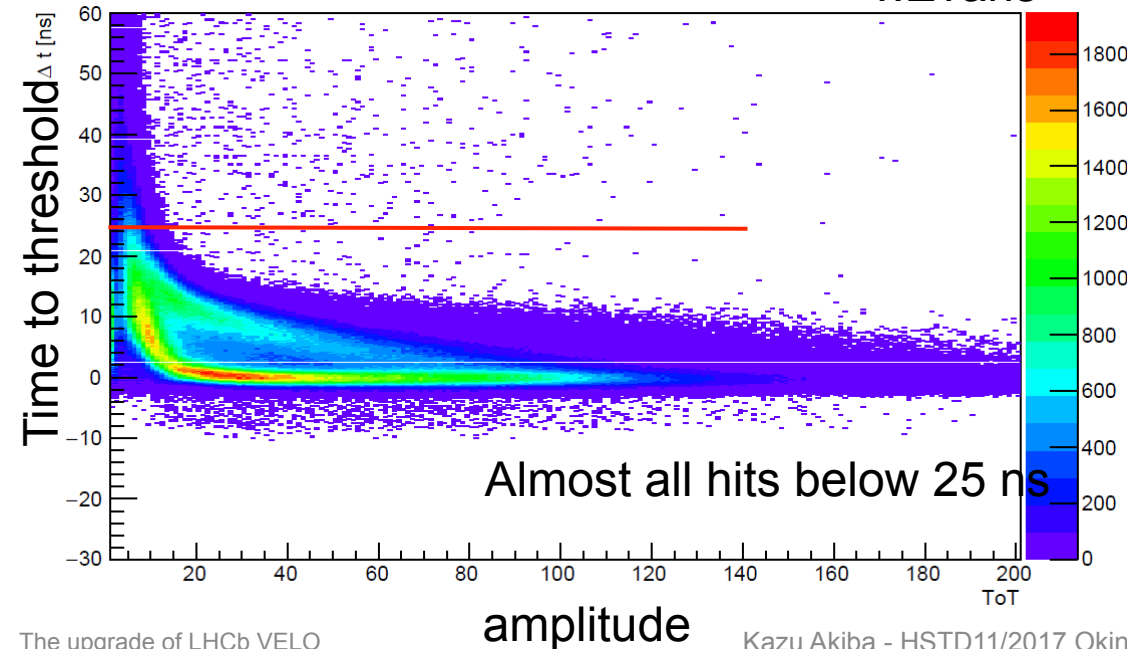
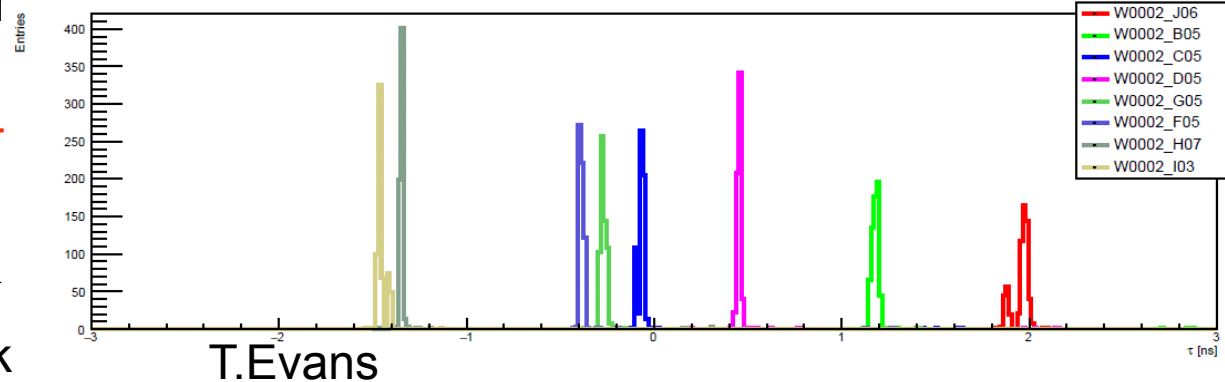
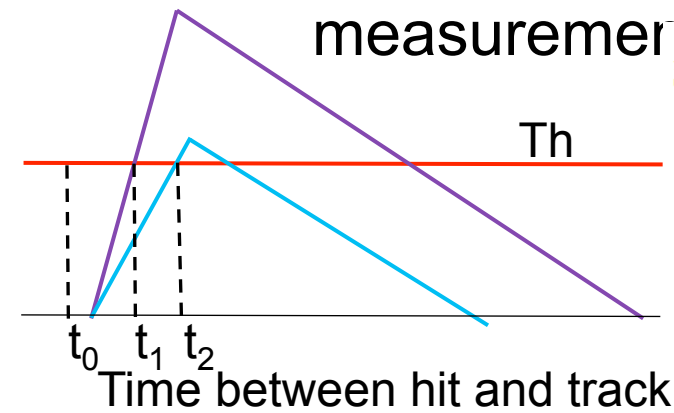


- n-in-n or n-in-p, 150/200 um
- Baseline of 450 um guard ring
- Reduced width guard rings (150um) and overlapping guard rings on backside in n-in-n case
- Irradiation and test beam program to validate Sensor and ASIC tech at high rates.

# Timing

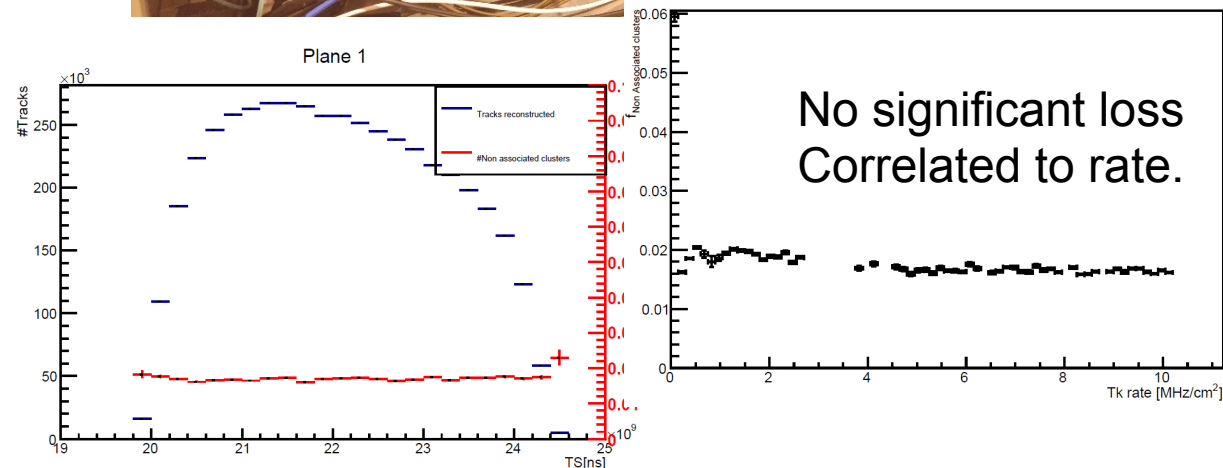
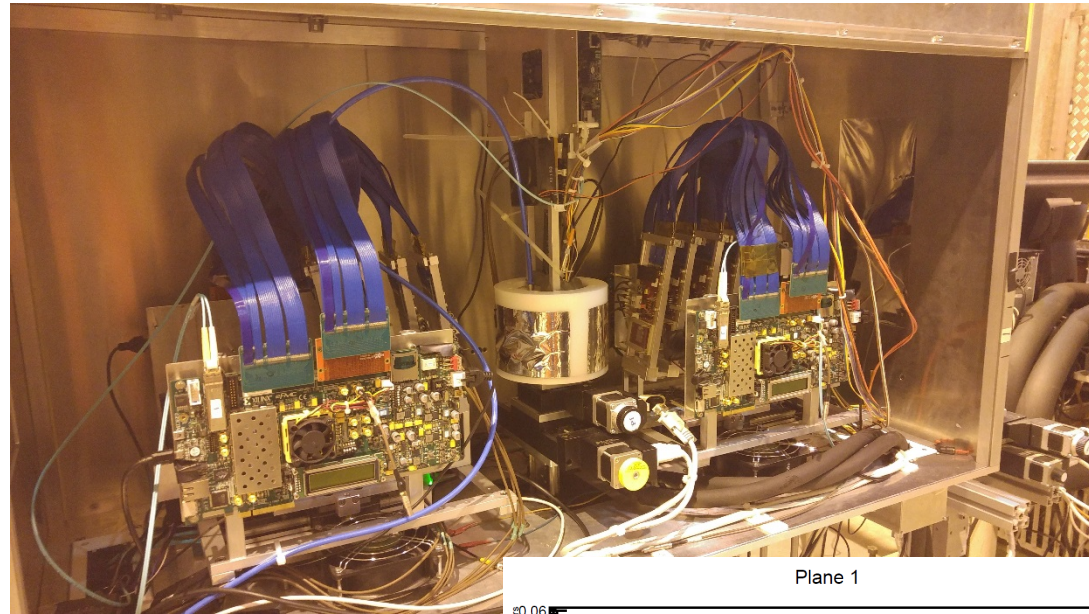
- Telescope has a very stable and precise time measurement

- Single TPX3 measurement resolution measured to 1 ns and telescope down to 0.4 ns.



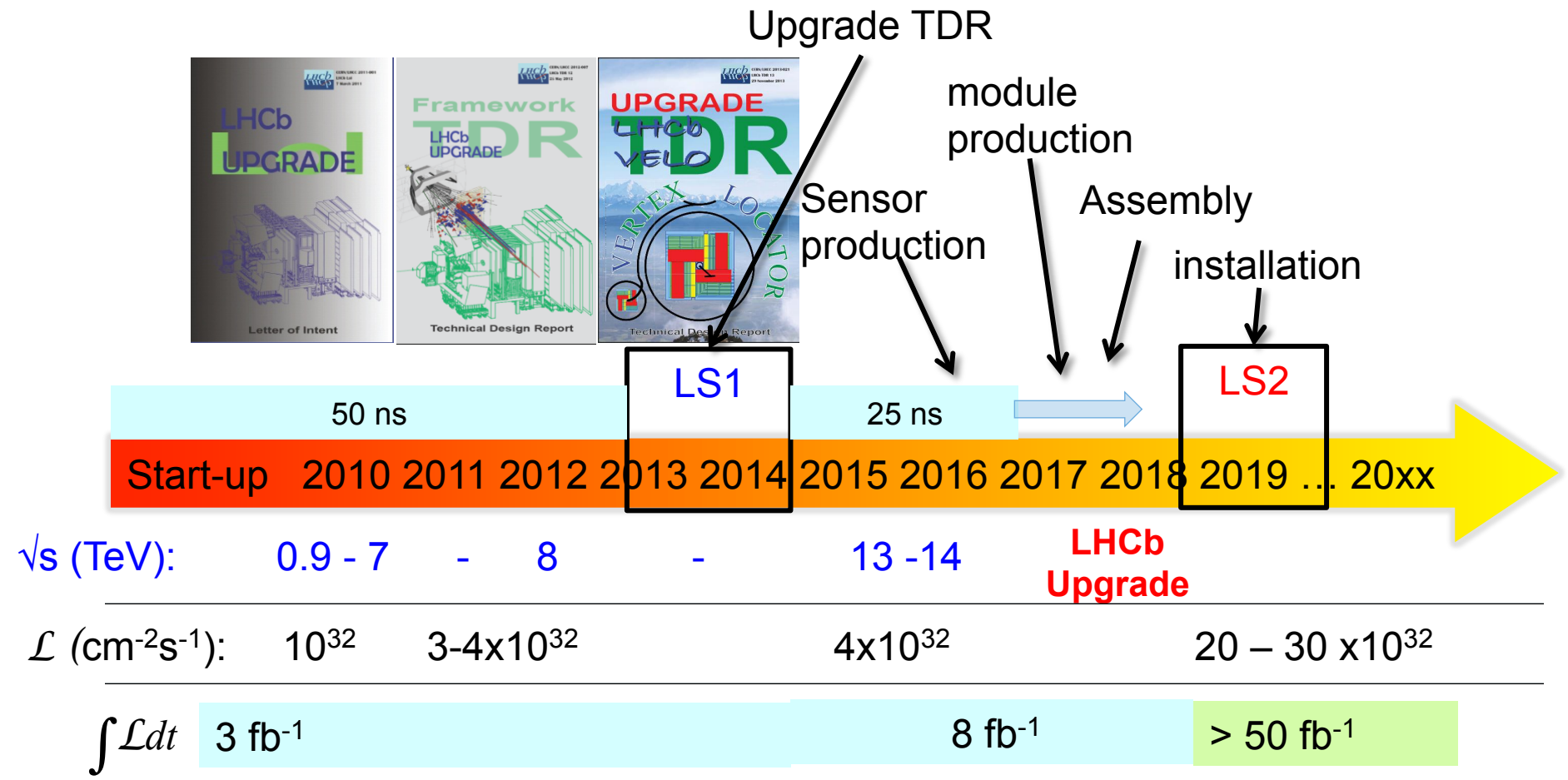
# The Telescope – our infrastructure.

- The **Timepix3** telescope is **fast, precise**, and easy to combine with **Timepix3** DUTs.
- The software is written in Gaudi architecture: Kepler.  **$\sim 15k$  tracks/s**.
- **Charge** measurement and clustering give a great pointing resolution  $\rightarrow$  down to  **$2\ \mu m$** .
- Precise **time stamps** make it simple and clean for the PatRec.
- Tracks can be measured with  **$0.4\ ns$  timing precision**
- We have operated up to  **$10\ Mtracks/s/cm^2$** .



A.DosilSuarez

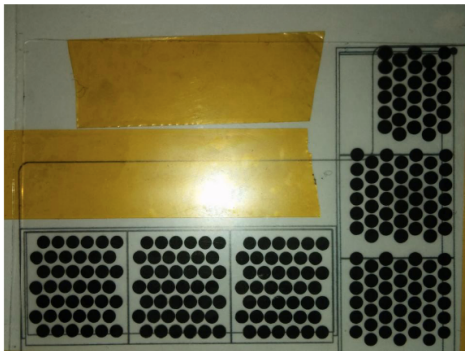
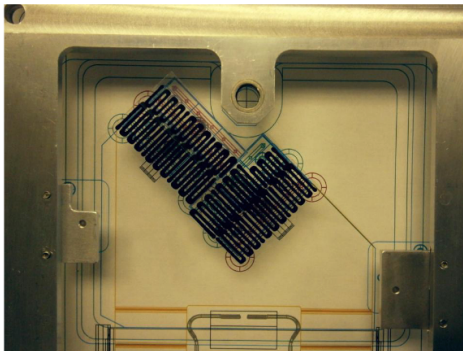
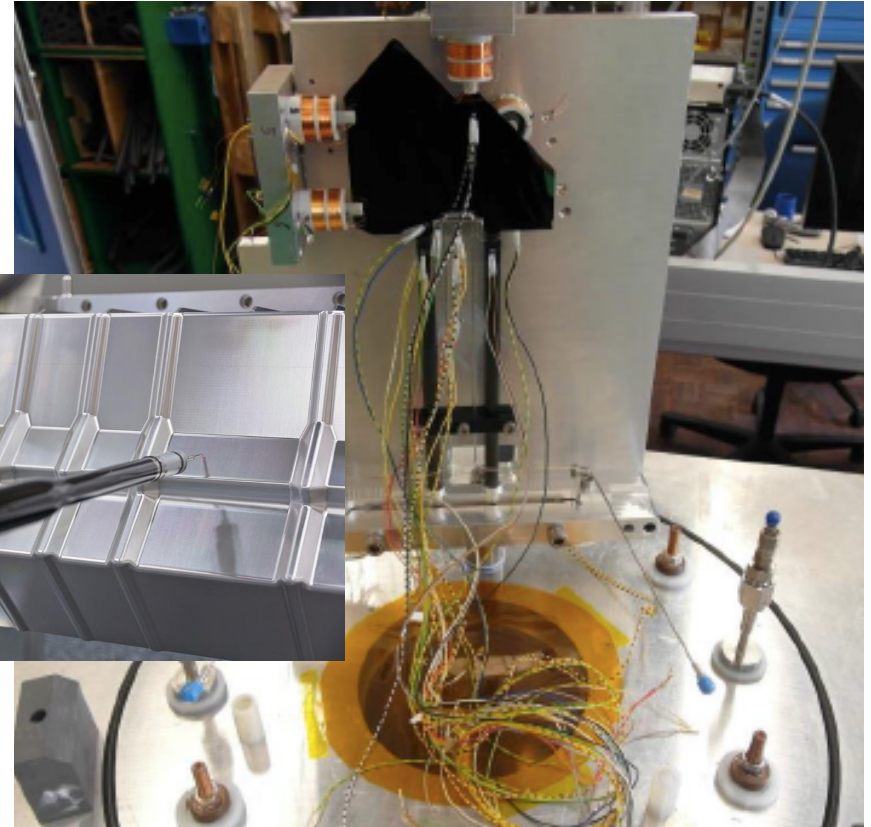
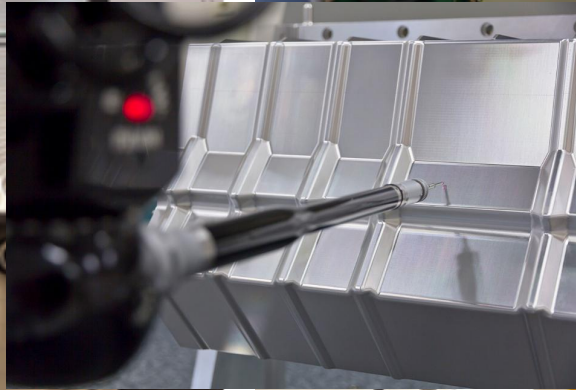
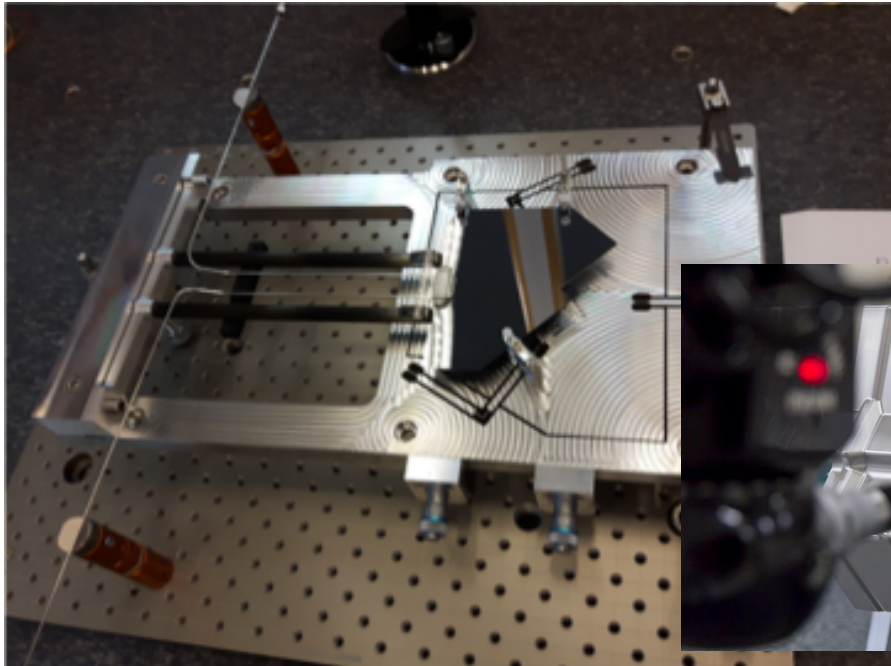
# Timeline



Current upgrade plan still compatible with post LS3 ...

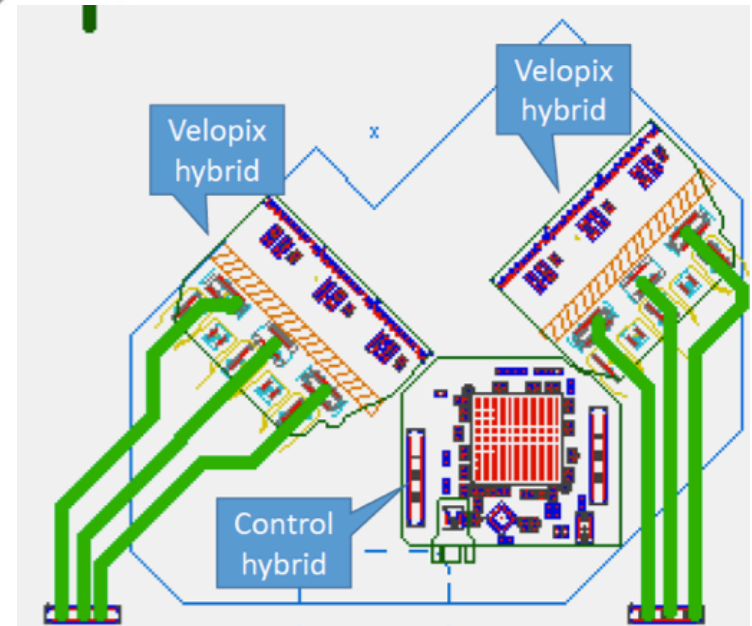
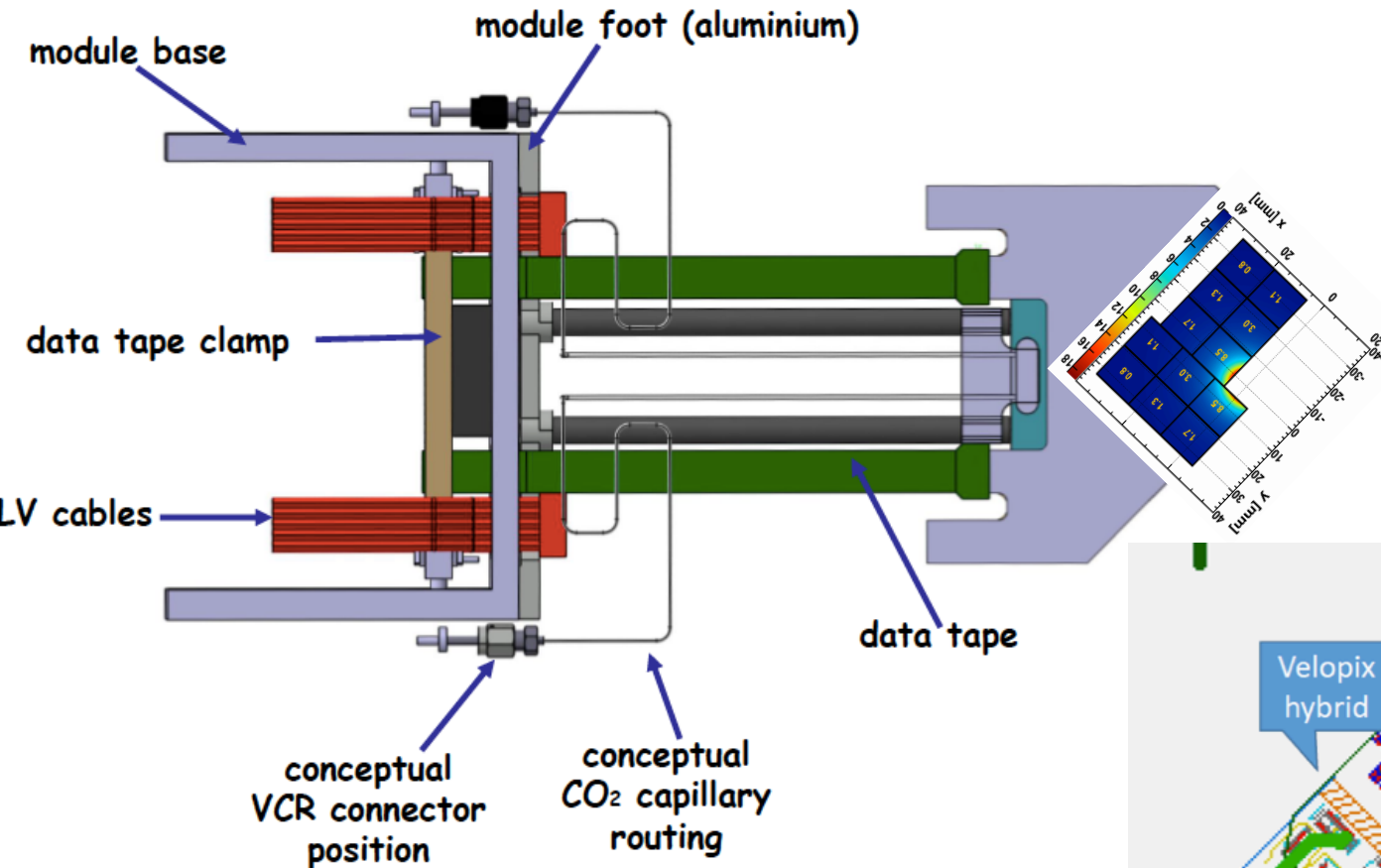


# Module prototypes



*The modules will be produced in both Nikhef and Manchester University*

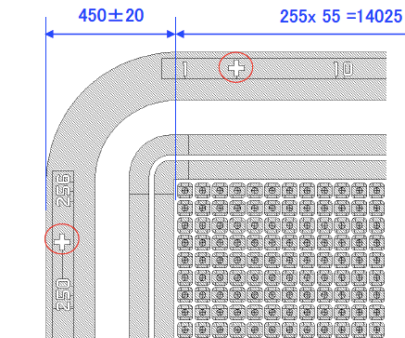
# Modules: 52 @ 25mm pitch (along beam)



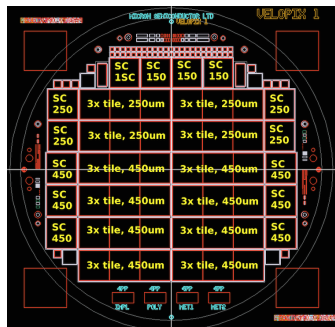
# Sensor Production

- ✦ Sensor corners to be rounded to optimise foil clearance
- ✦ Implant width: 39  $\mu\text{m}$  chosen – better efficiency

300V:  
Underdepleted



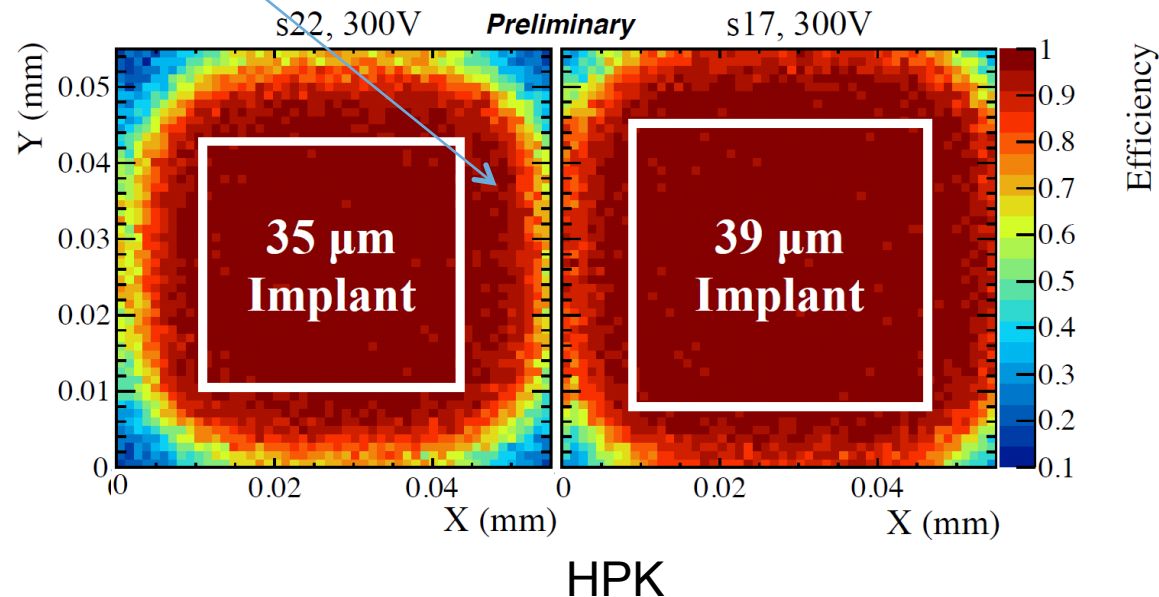
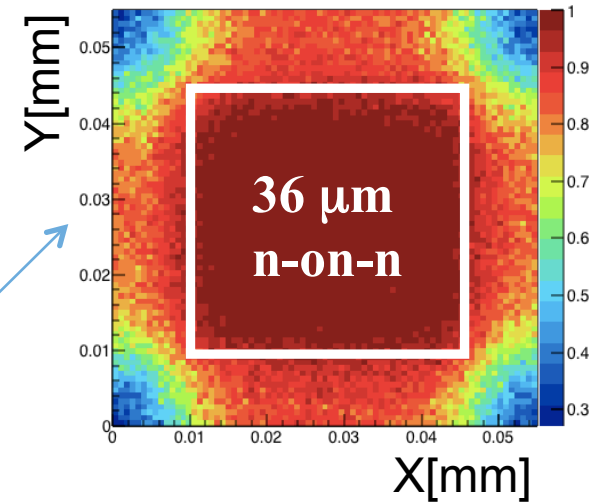
Mask detail  
Under Production  
at HPK



Mask detail  
Under Design  
at Micron

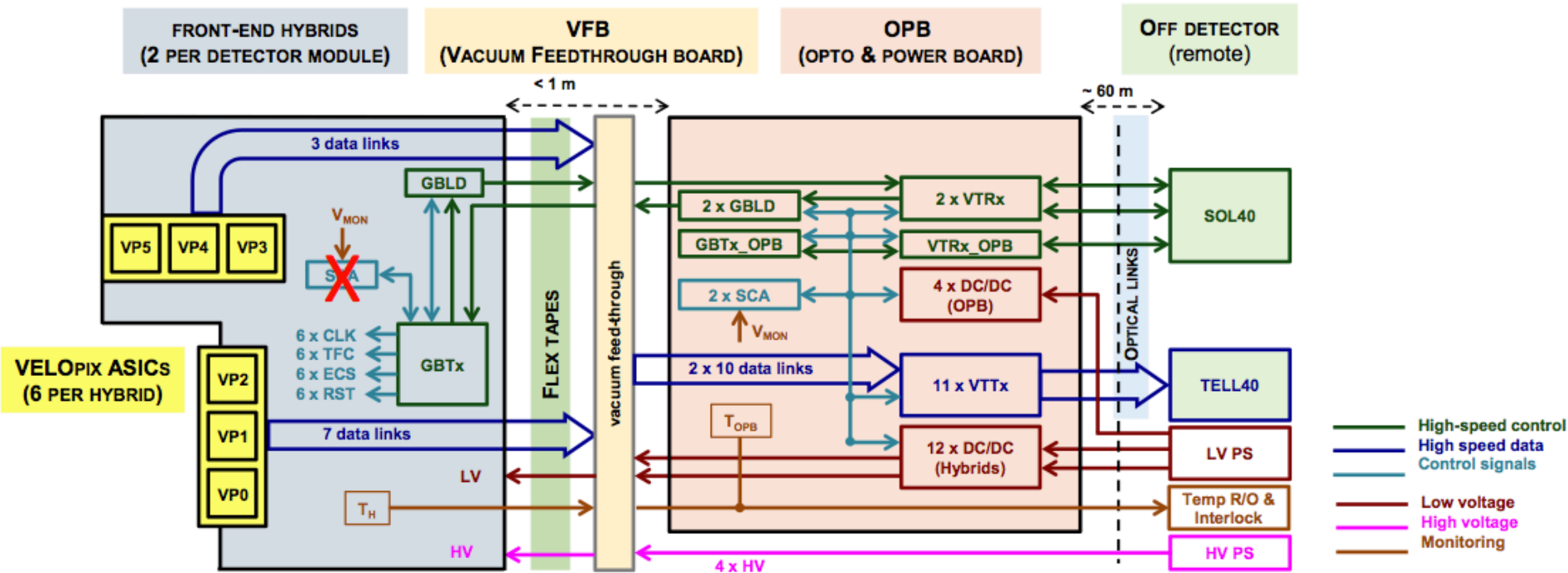
Intrapixel Efficiencies

Micron



# Electronics chain: overview

Many common LHCb elements



- 48 copper links from chips.
- Electrical to optical conversion outside of vacuum tank → 20 Optical links ~5 Gbit/s each
- 1 FPGA to reads out 1 module

VELO specific components involve:  
data transmission,  
backend data acquisition and  
Time reordering of hits/clusters.